



Normal-conducting high-gradient rf systems

Part 2



Lecture structure



1. Basic concepts of travelling wave accelerating structures
2. High peak rf power production and manipulation
3. High field phenomena in accelerating structures

Now – The thrilling world
of high gradients!



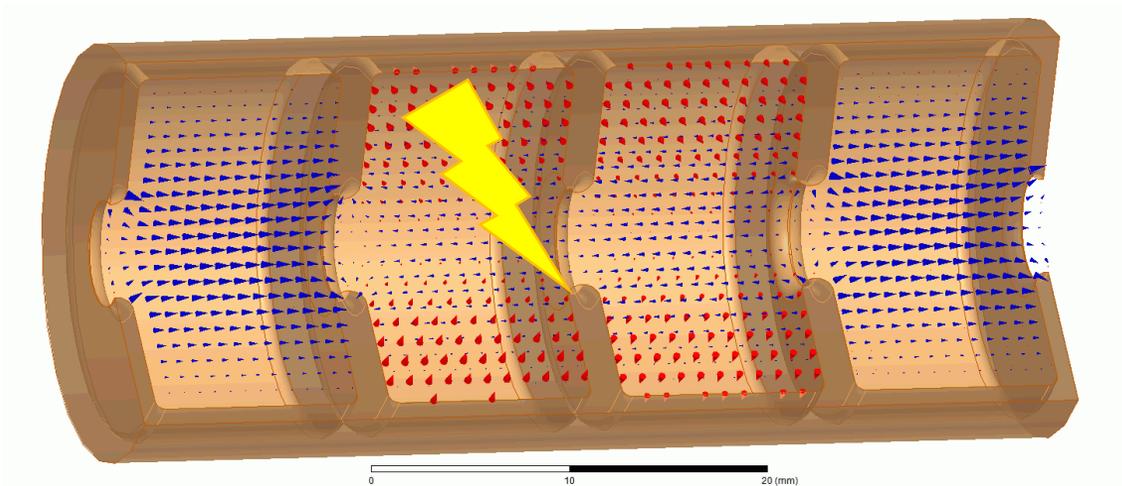


Complexity



- The underlying equations for the acceleration equations we have seen are Maxwell's equations and the Lorentz force – linear equations!
- When we raise the power we put in a structure, increasing the surface fields, we encounter a whole range of new phenomena.
- These phenomena include field emission and vacuum arcing and pulsed surface heating which, in various combinations, affect the beam and can damage a structure.
- We need to consider:
 - Electromagnetism
 - Material science
 - Plasma physics
 - Quantum mechanics - field and photo emission

Vacuum arc, a.k.a. breakdown



Some (round) numbers to keep in mind:

Average accelerating gradient - 100 MV/m

Peak surface electric field – 220 MV/m

Input power - 50 MW

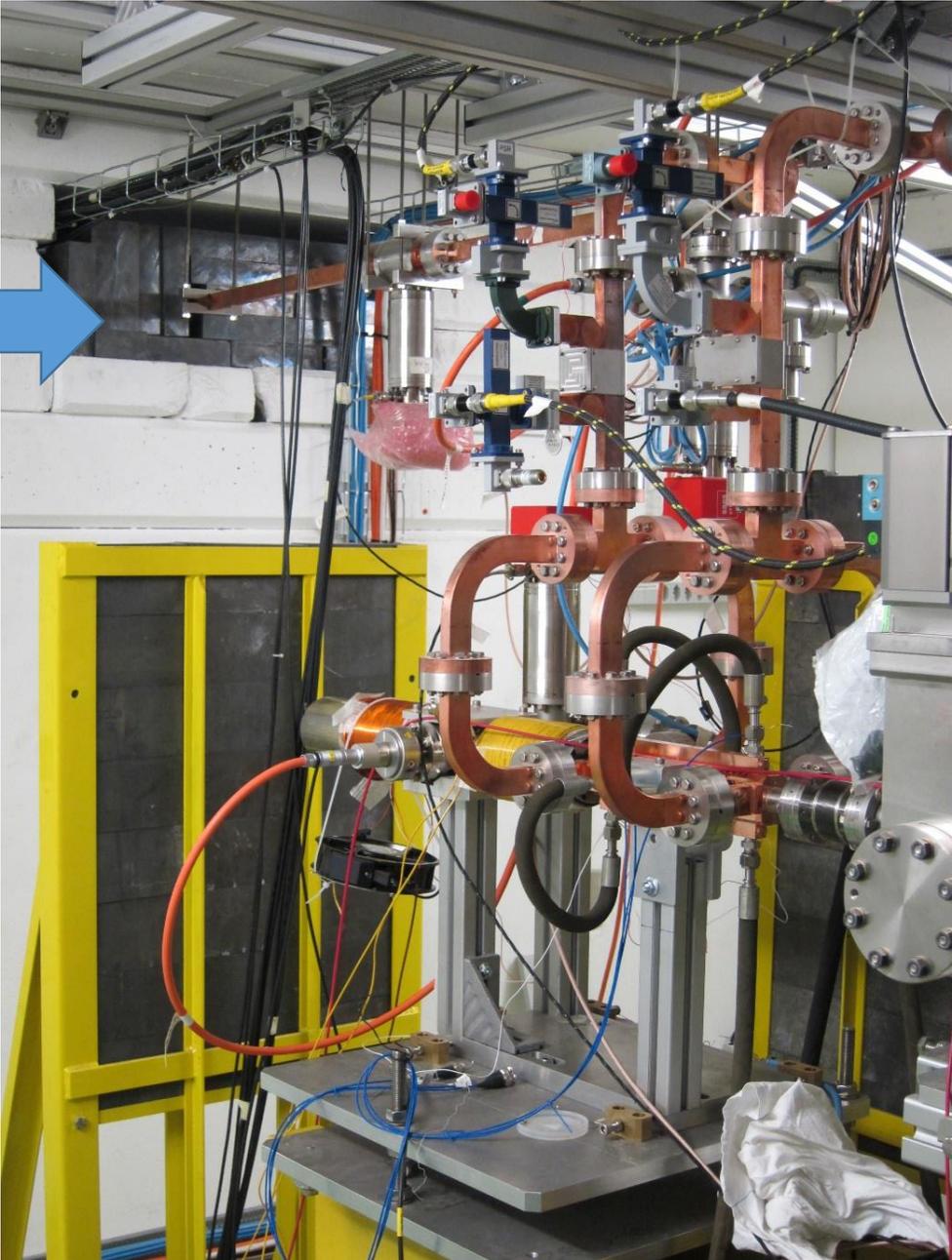
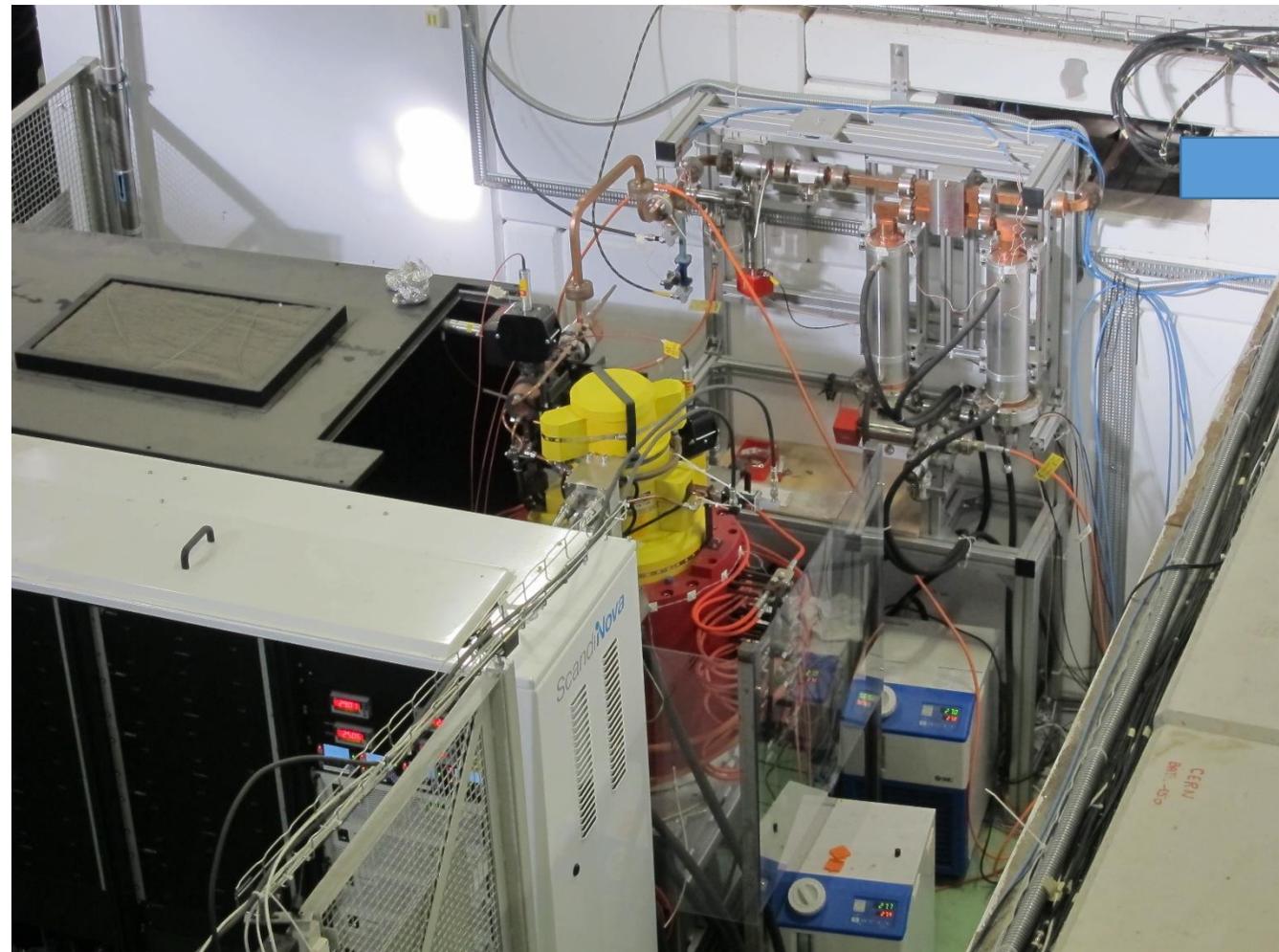
Pulse length - 180 ns

Pulse energy of 12 J.

How do we experience breakdown in an rf system?
First introduce system.



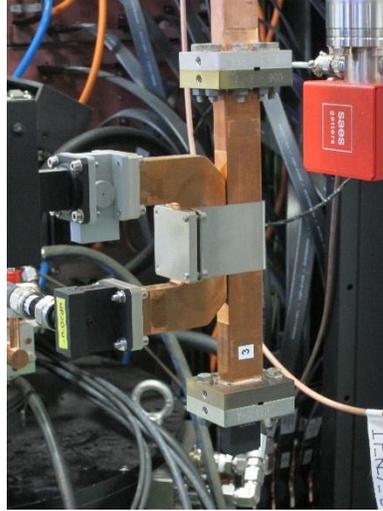
This klystron modulator unit feeds...



this accelerating structure.



klystron



directional coupler



load

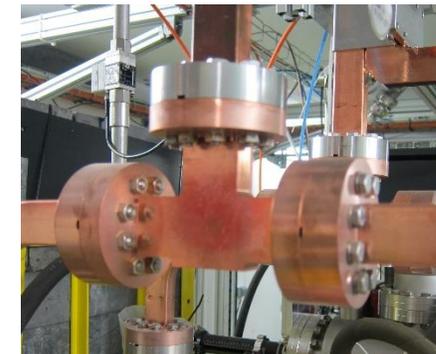
Reflected

Incident

Transmitted

splitter

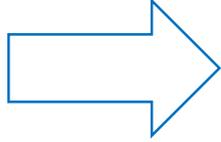
accelerating structure



The basic layout of an rf system



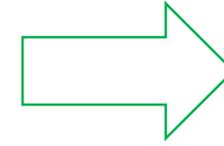
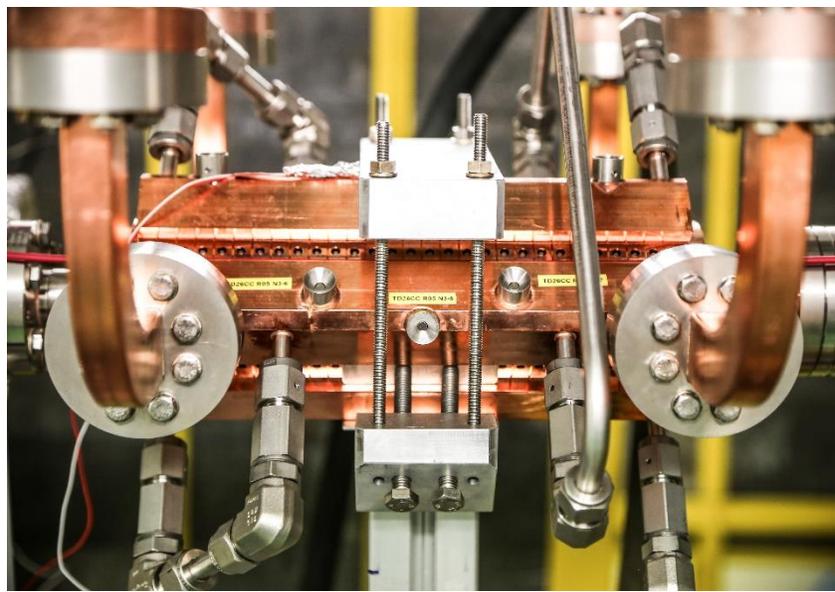
incident power



rf signals



reflected power



transmitted power

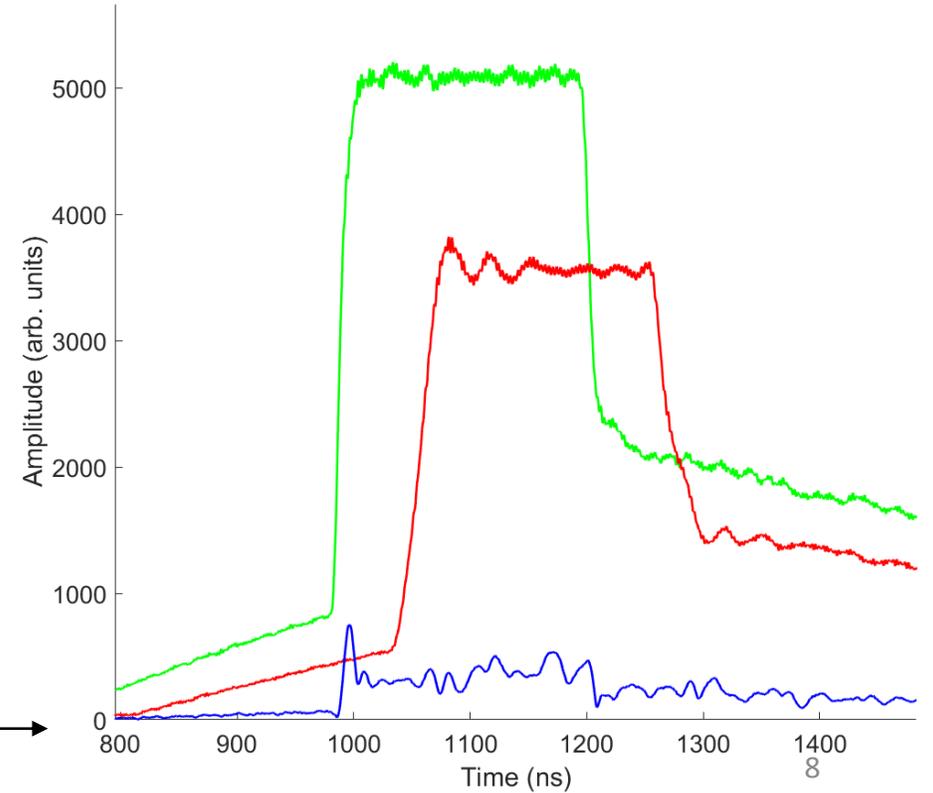
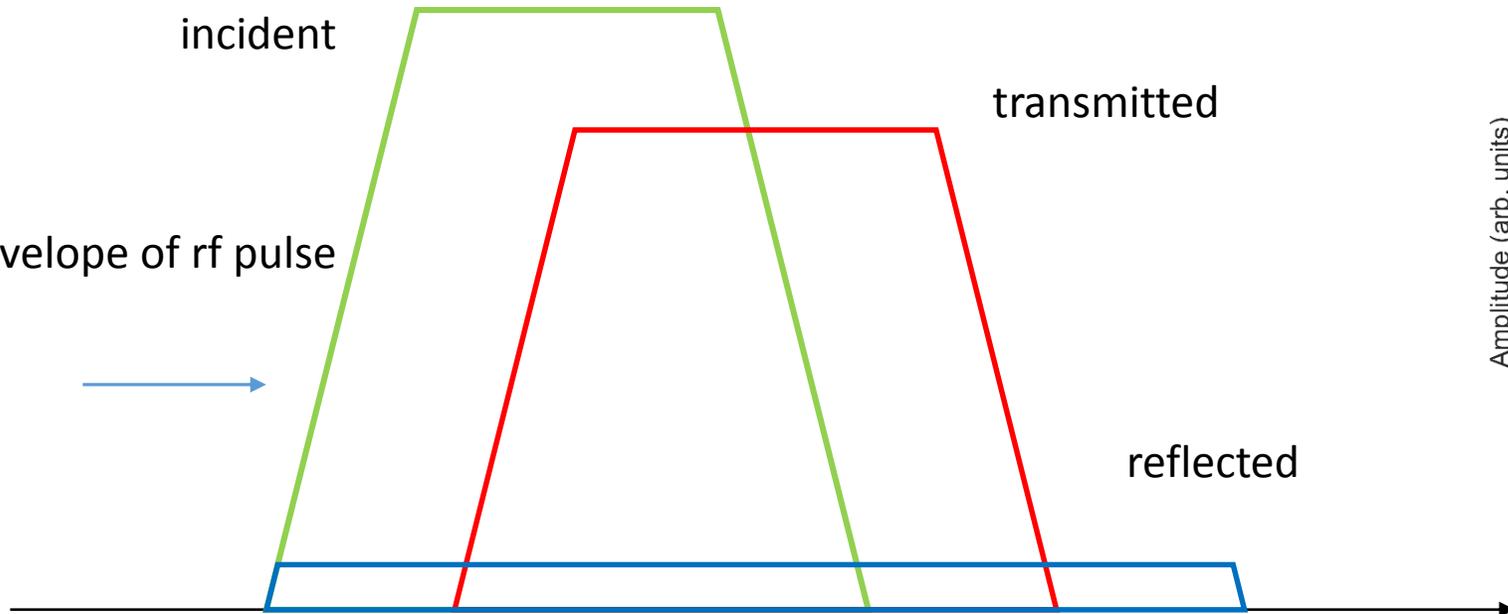
From CLIC XBoxes

incident

transmitted

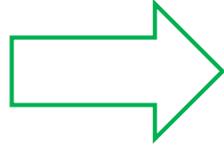
reflected

Envelope of rf pulse





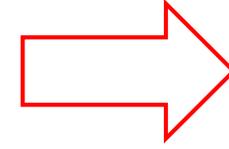
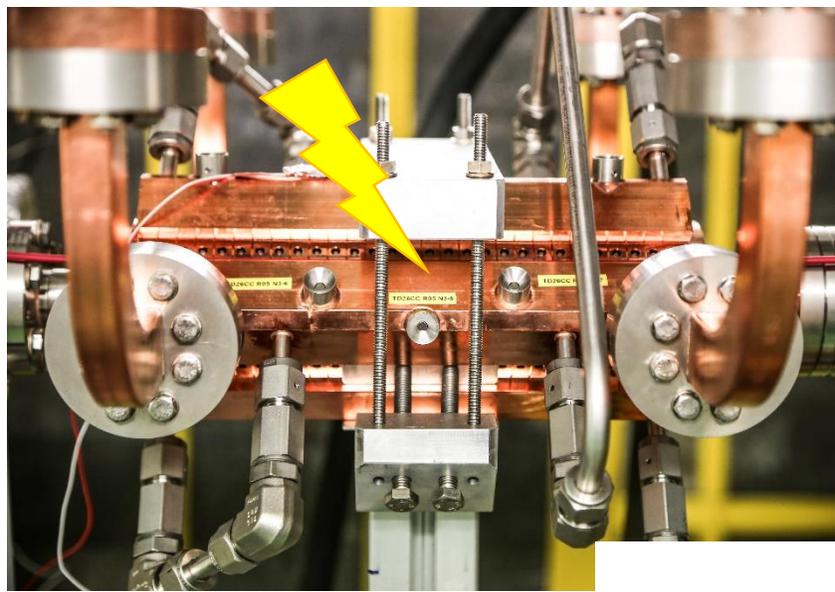
incident power



rf signals



reflected power



transmitted power

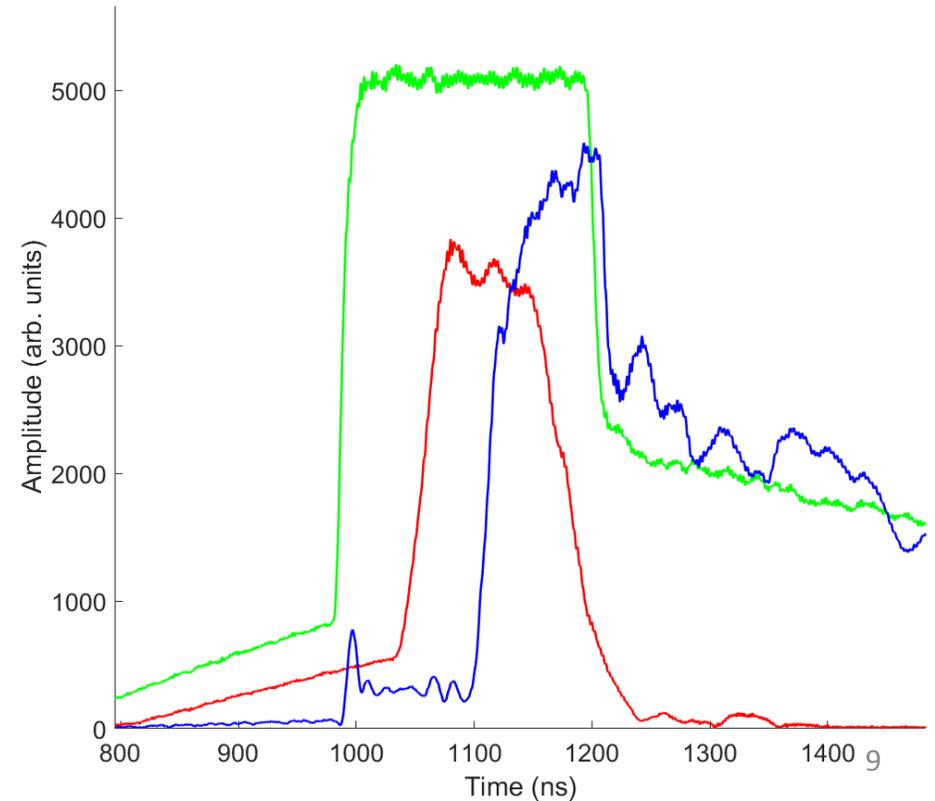
incident

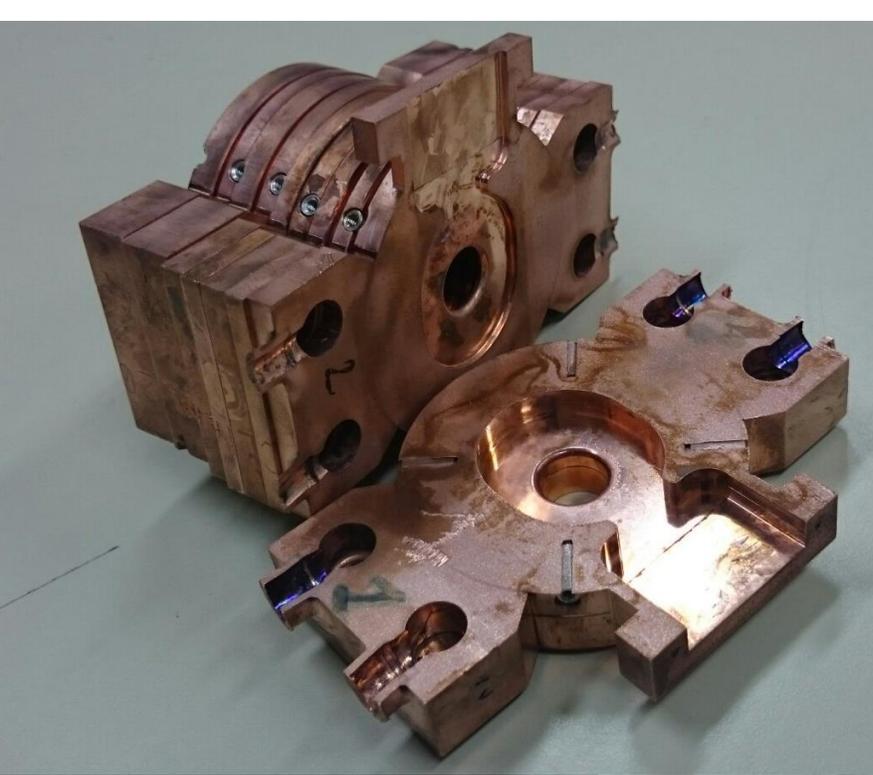
Suppression of transmission and reflection due to breakdown

transmitted

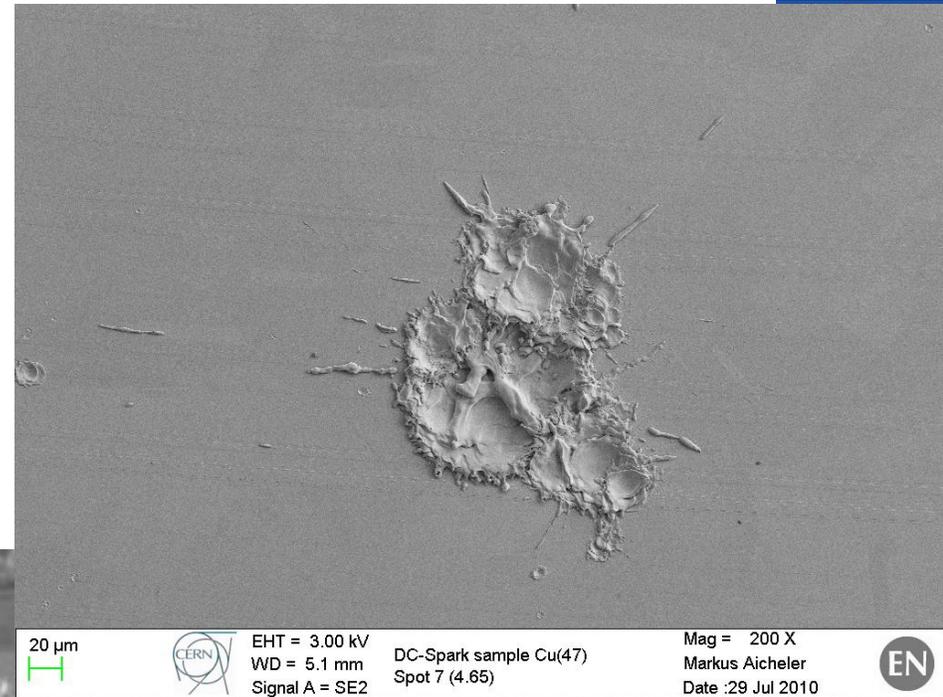
reflected

CAS on Future Colliders, 4 and 5 March 2018

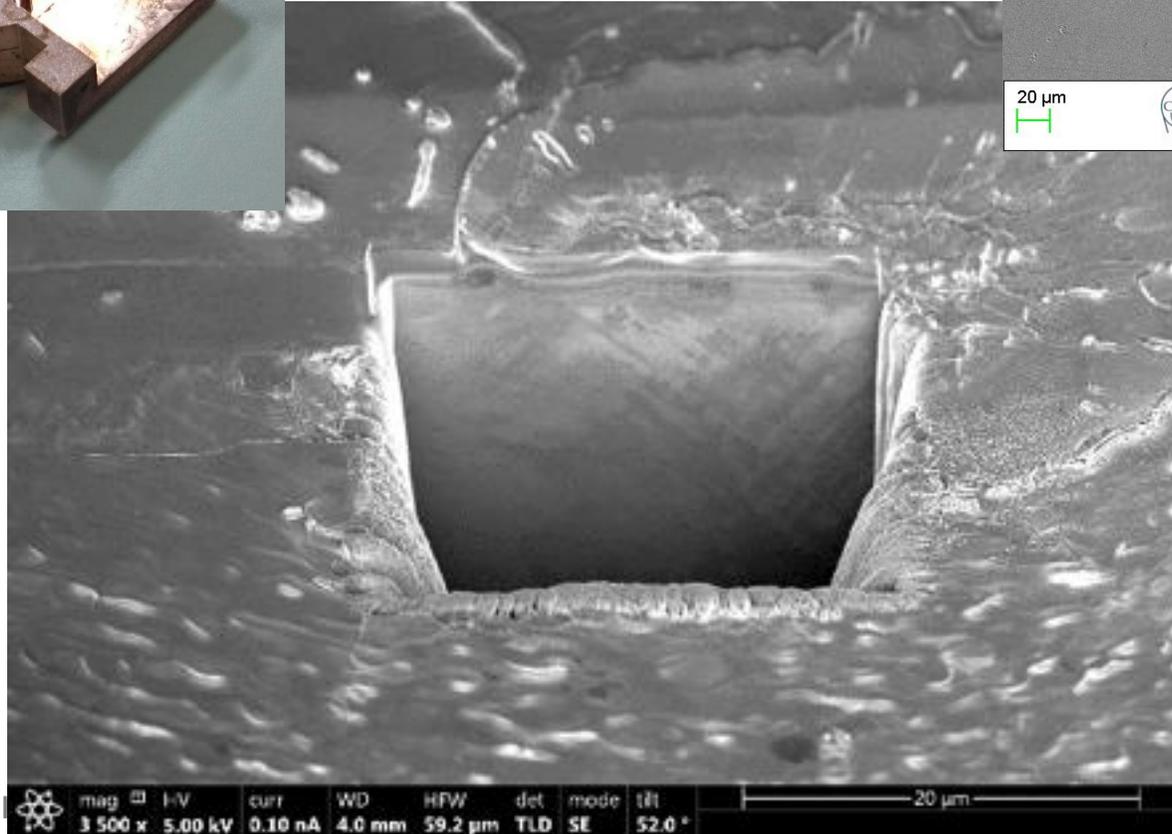




And with
electron
microscopy



20 µm
EHT = 3.00 kV
WD = 5.1 mm
Signal A = SE2
DC-Spark sample Cu(47)
Spot 7 (4.65)
Mag = 200 X
Markus Aicheler
Date :29 Jul 2010
EN



mag 3 500 x
I-V 5.00 kV
curr 0.10 nA
WD 4.0 mm
HPW 59.2 µm
det TLD
mode SE
tilt 52.0°



CLIC klystron-based X-band test stands around the world



XBox-1: 50 MW, 50 Hz



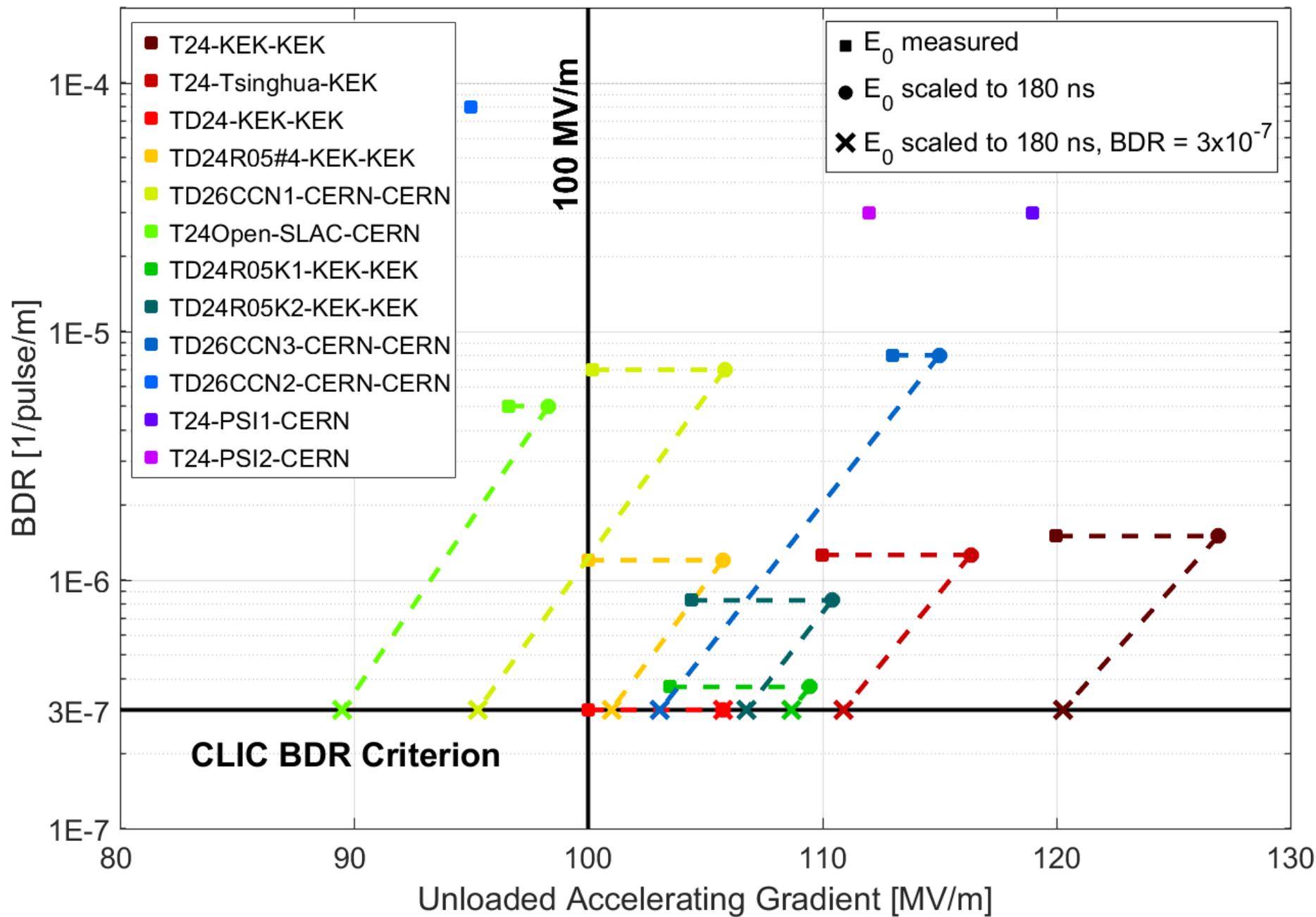
XBox-2: 50 MW, 50 Hz



XBox-3: 50 MW, **400 Hz!**

NEXTEF
KEK







Overview

Here is an overview of the breakdown process and the big questions so you have context as the lecture proceeds.

Breakdown is highly complex and multi-scale phenomenon so we need to zoom in and out of the problem – nm to mm, nsec to μ sec, nA to 100 A etc.

We also need to look at practical effects and their physical explanation.

Breakdown steps:

- Applied electric field causes electron and neutral atom emission from cathodic surfaces.
- This emission is concentrated at sites which are surface features and, in the early stages of operation, contaminants.
- Electrons ionize neutral atoms.
- Ions are accelerated back to the cathode.
- The ions sputter more, starting avalanche that leads to a plasma just above surface.
- Plasma sheath forms, setting up multi GV/m surface fields and strong electron emission.
- Electrons interfere with rf transmission.

Some of the big questions:

- Why does gradient and surface field depend so much on rf geometry?
- What is evolving during conditioning and what exactly is getting better?
- What is the origin of breakdown rate vs gradient and pulse length dependencies?
- What is the nature of the sites which will lead to breakdown?
- What drives the statistics of breakdown occurrence?
- What is the nature of the breakdown sites and what is the origin of the β correction?



Dependence of gradient on rf geometry

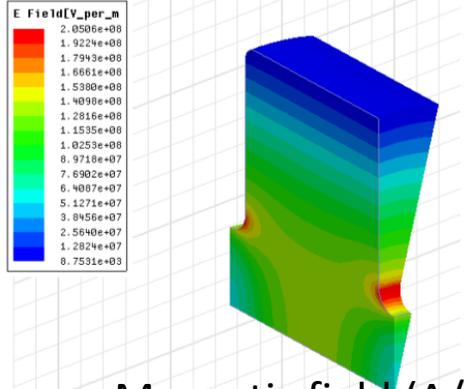
- Different design structures achieve different gradients. Big question for us have been:
 - Can we quantify the dependence of achievable accelerating gradient on geometry?
 - Where does such a geometrical dependency come from?
- Trying to understand, derive and quantify geometrical dependence has been a significant effort because an essential element of the overall design and optimization of the collider, especially through interaction with beam.
- You might think that breakdown is determined by surface electric field, but it turns out to be more complicated than that.



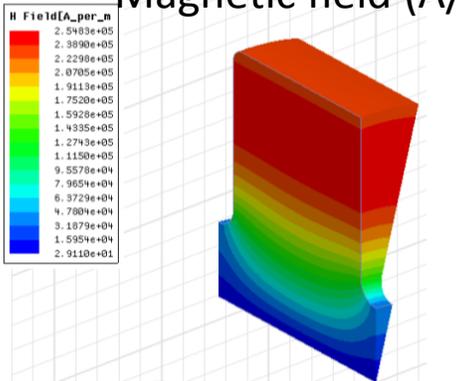
Geometric dependency



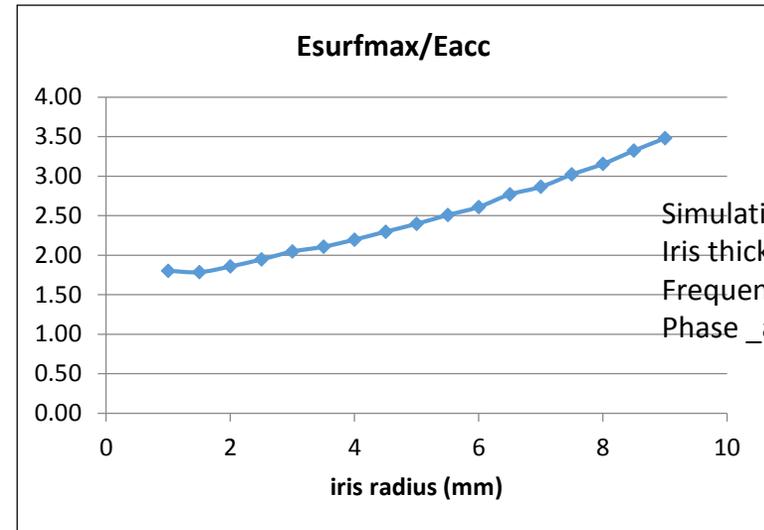
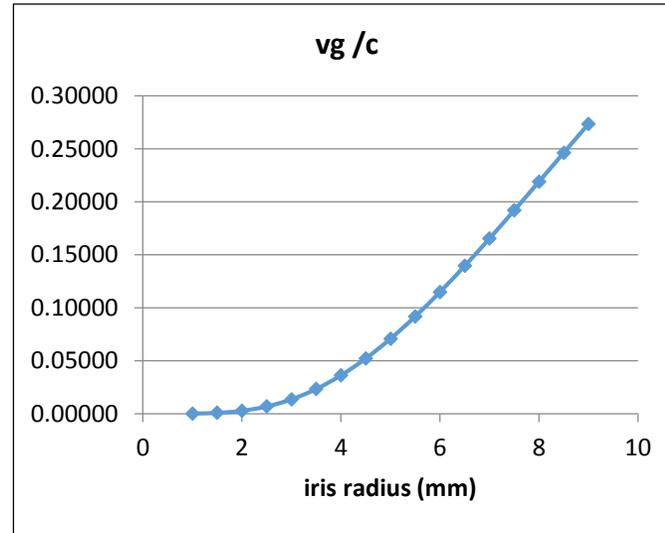
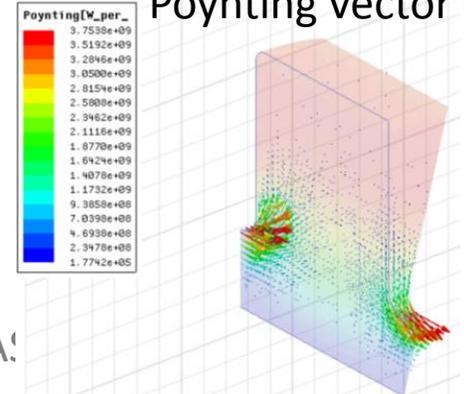
Electric field (V/m)



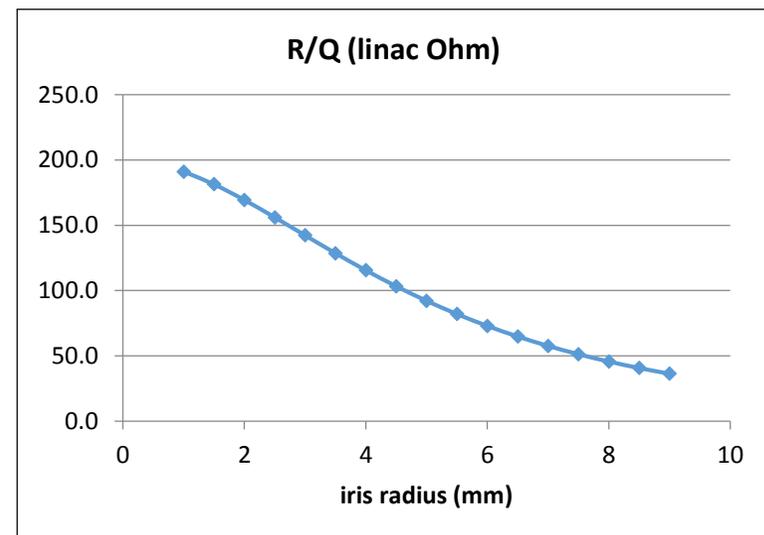
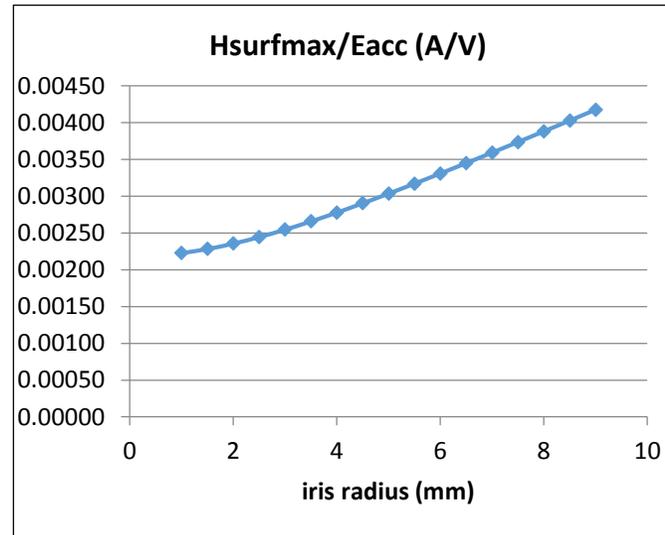
Magnetic field (A/m)



Poynting vector (W/m²)



Simulation in HFSS12
 Iris thickness: 1.66mm
 Frequency: 11.424GHz
 Phase_adv/cell: 120 degree

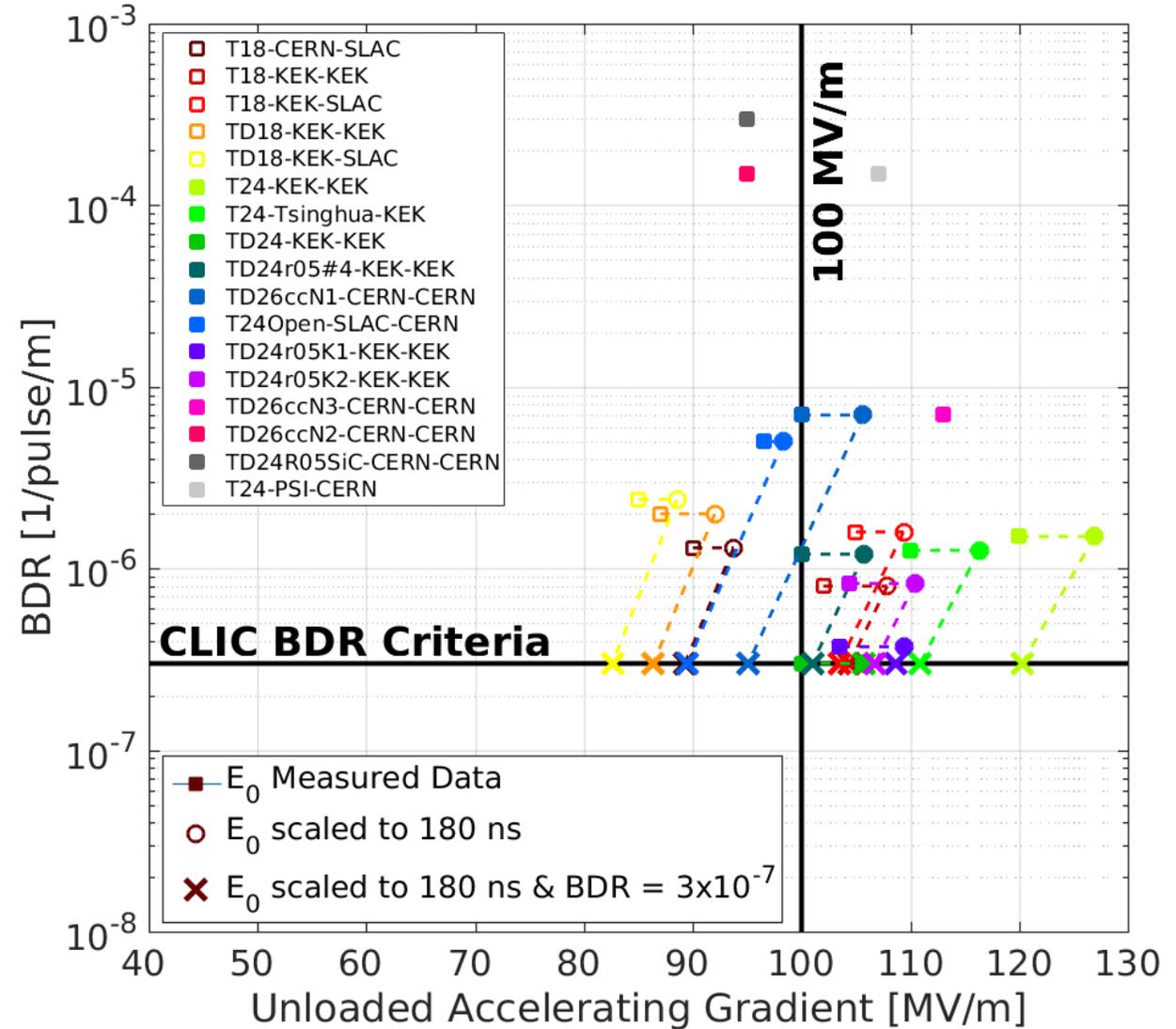




Performance of two different series of structures.

The important point is that the accelerating gradient, and maximum peak surface electric field is different at the end of the tests.

When including more structures, the effect is even more pronounced.





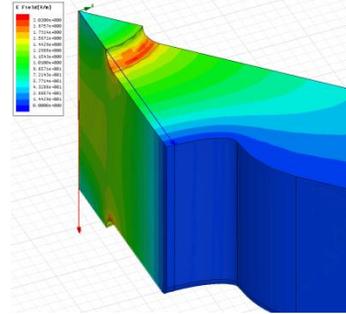
This has resulted in the development of two power-density based design criteria:



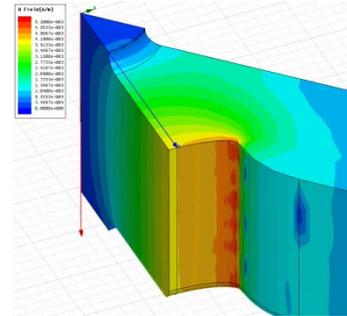
$$\frac{P}{\lambda C} = \text{const}$$

global power flow

$$E_s/E_a$$



$$H_s/E_a$$



$$S_c = \text{Re}(\mathbf{S}) + \frac{1}{6} \text{Im}(\mathbf{S})$$

local complex power flow

$$S_c/E_a^2$$

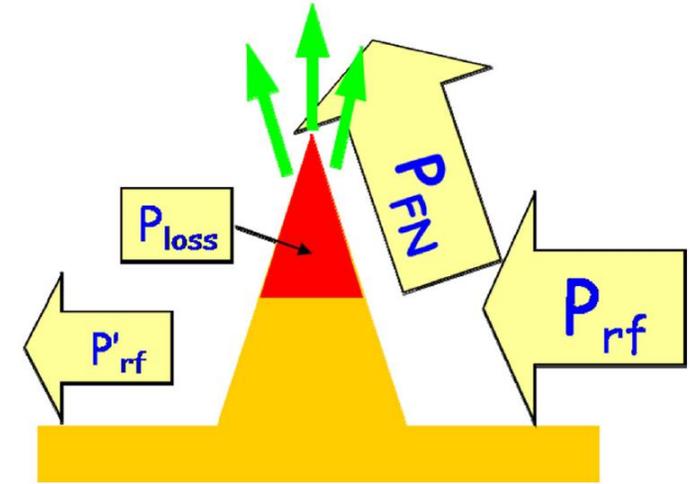
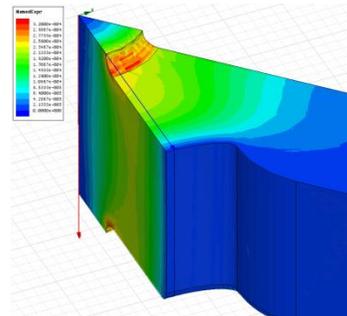


FIG. 9. (Color) Schematic view of the power flow balance near the tip.

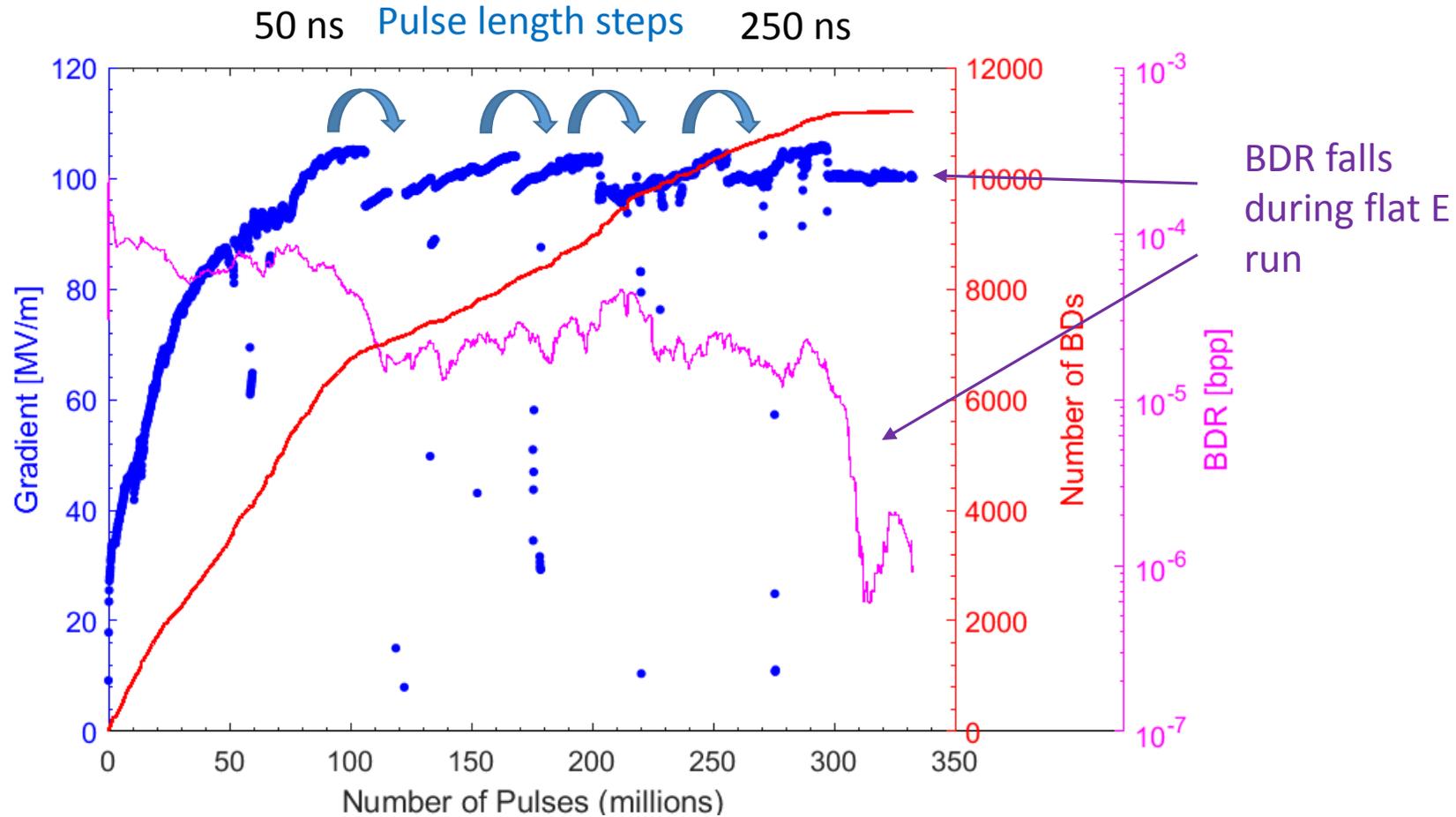
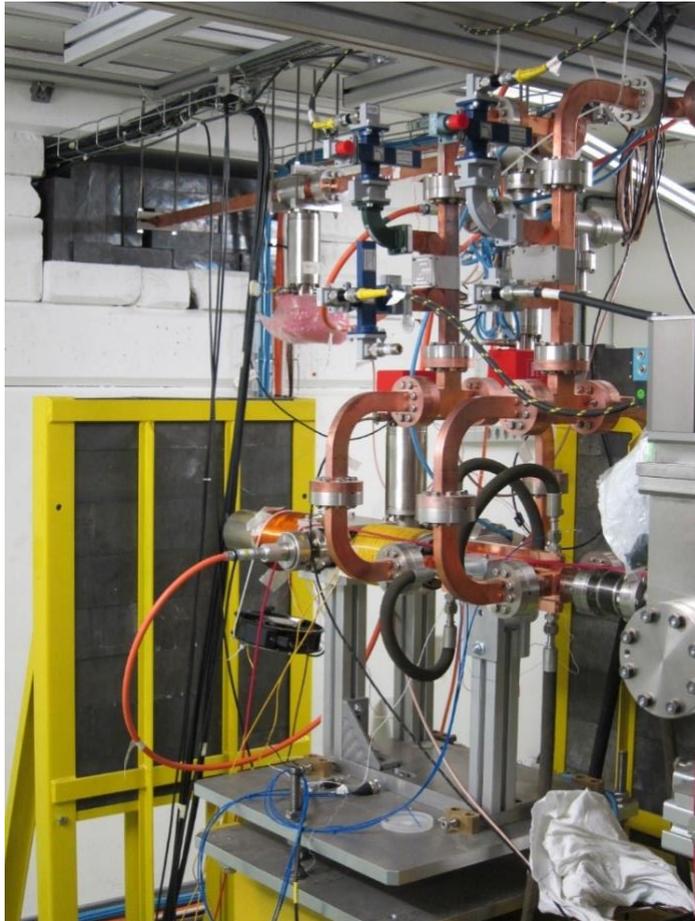
S_c is typically the quantity which dominates the design of high-gradient travelling wave structures.

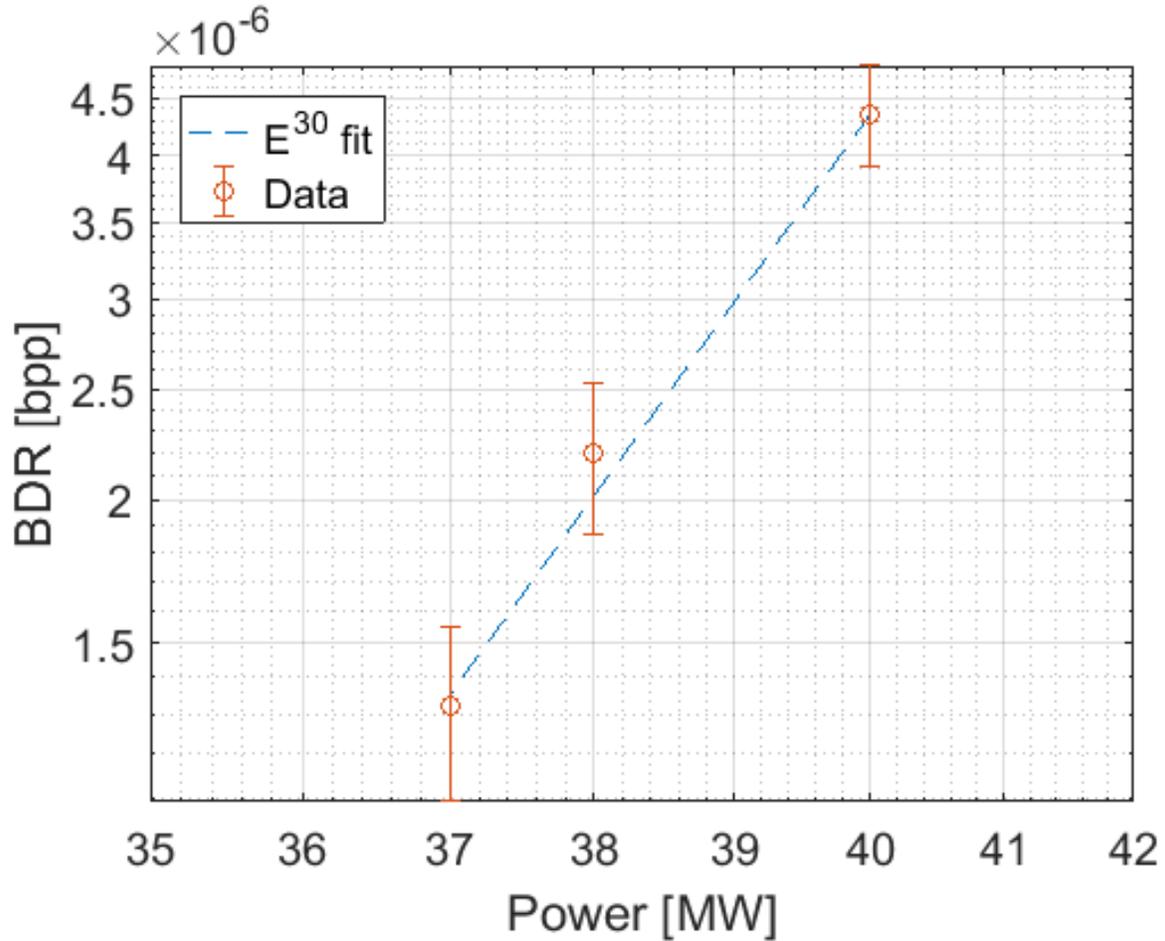
A. Grudiev, S. Calatroni, and W. Wuensch,
New local field quantity describing the high gradient limit of accelerating structures,
 Phys. Rev. ST Accel. Beams 12, 102001 (2009)



Conditioning

Accelerating structures do not run right away at full specification – pulse length and gradient need to be gradually increased while pulsing. Typical behaviour looks like this:





Data taken in XBox-2 with TD26CC structure, T. Lucas

Regularly observed dependence:

$$BDR \propto E^{30} \tau^5$$

Physical model based on defect formation



$$BDR \propto e^{\frac{-E^f + \epsilon_0 E^2 \Delta V}{k_b T}}$$

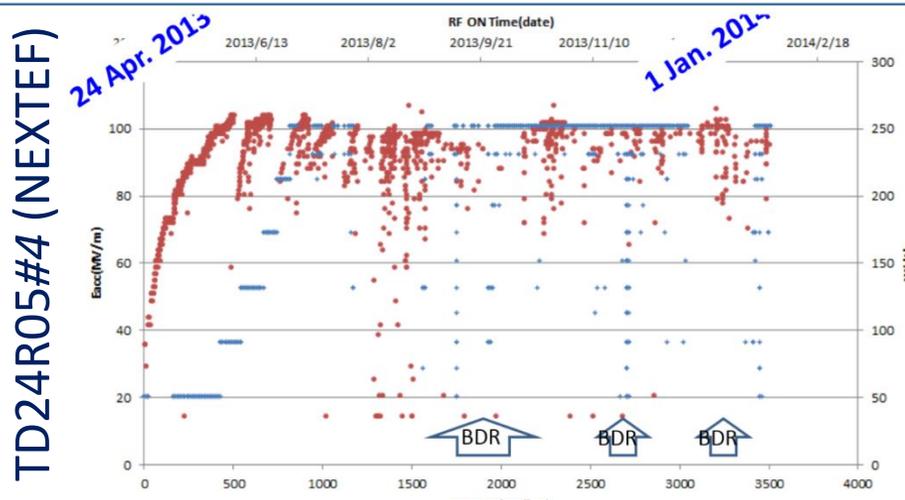
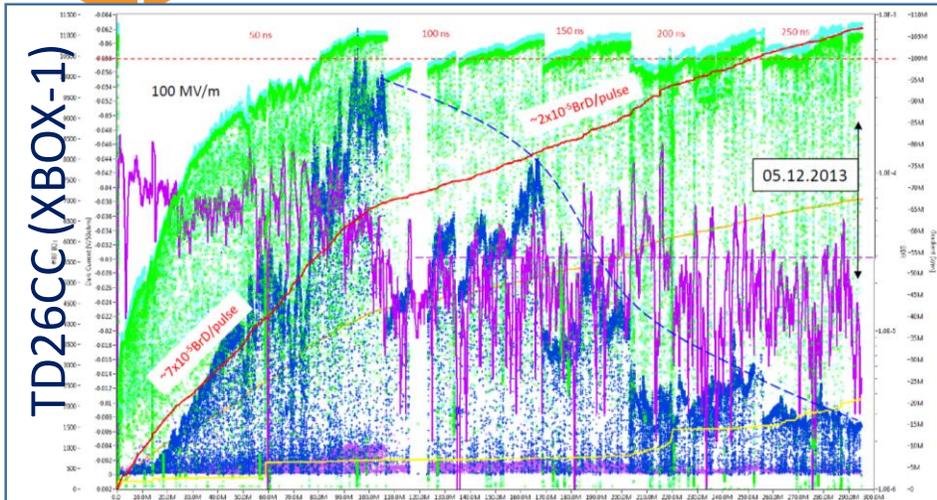
$$E^f = 0.8 \text{ eV}$$

$$\Delta V = 0.8 \times 10^{-24} \text{ m}^3$$

K. Nordlund, F. Djurabekova, *Defect model for the dependence of breakdown rate on external electric fields*, Phys. Rev. ST Accel. Beams 15, 071002 (2012)



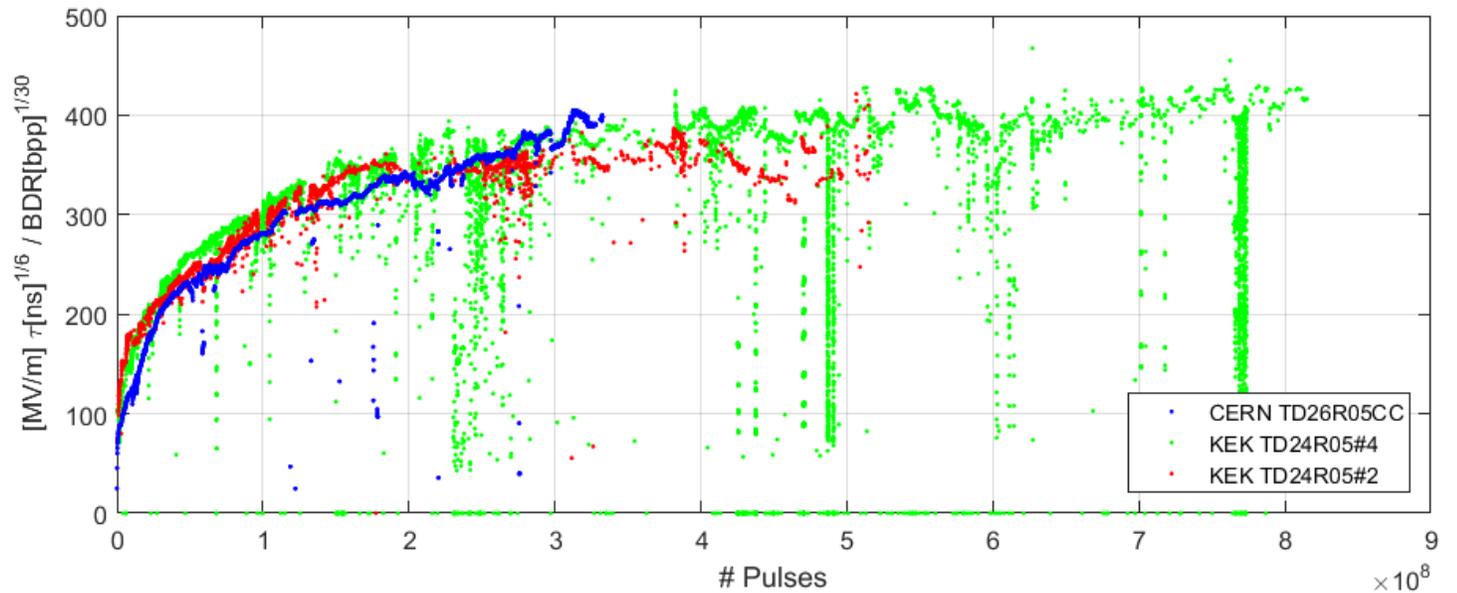
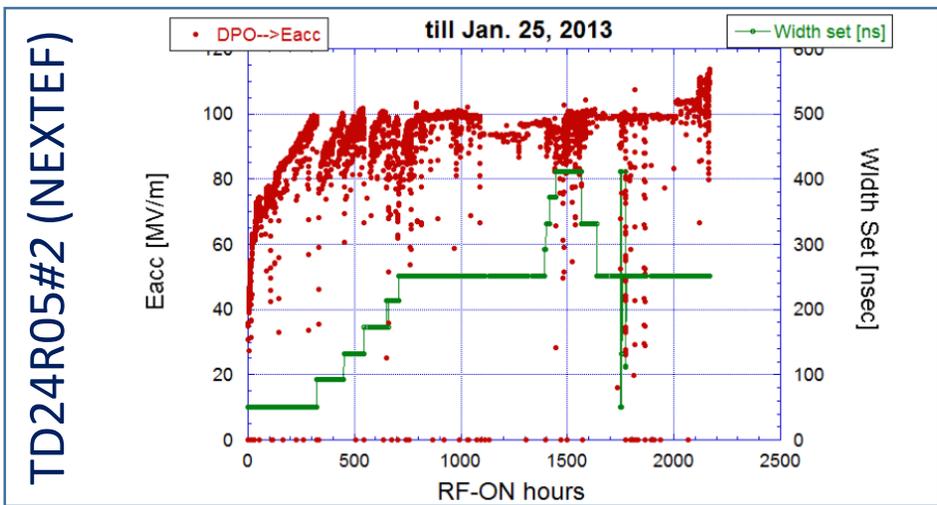
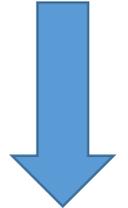
Comparison of three similar structures



We normalize by:

$$BDR \propto E^{30} \tau^5$$

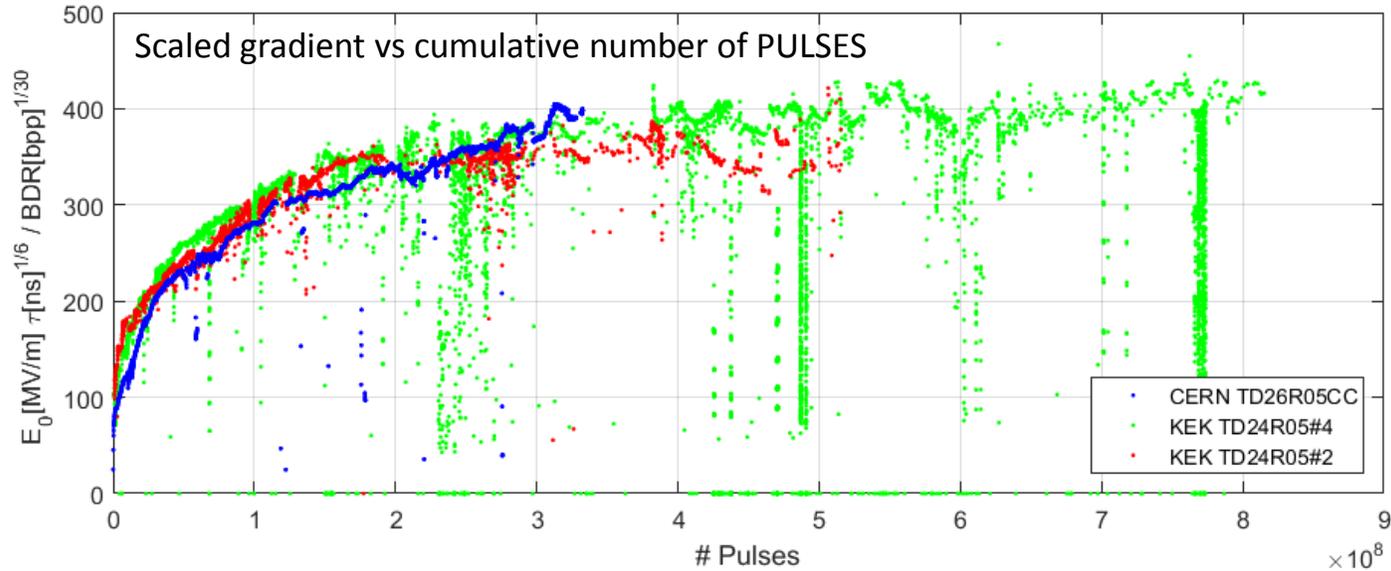
And get



Interpretation: Conditioning is a reproducible process which implies a well defined physical mechanism.

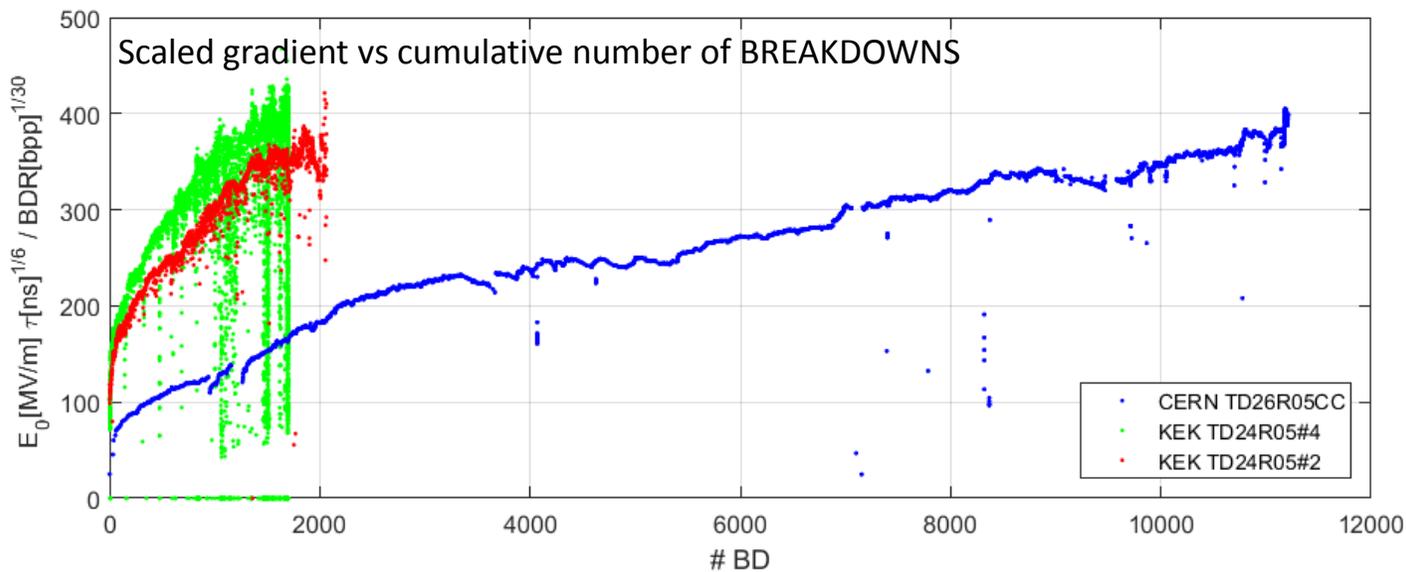


Comparing conditioning

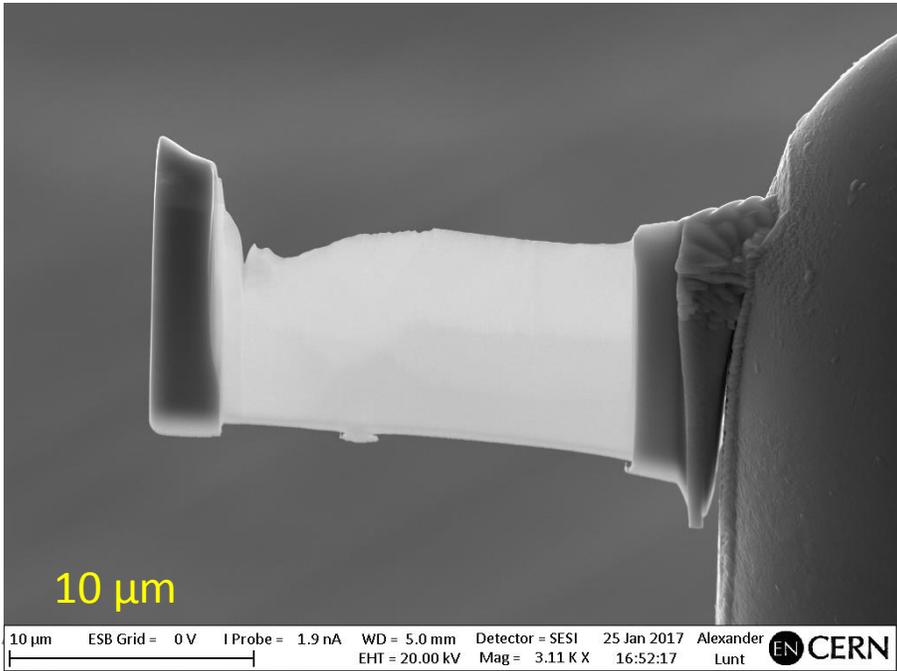
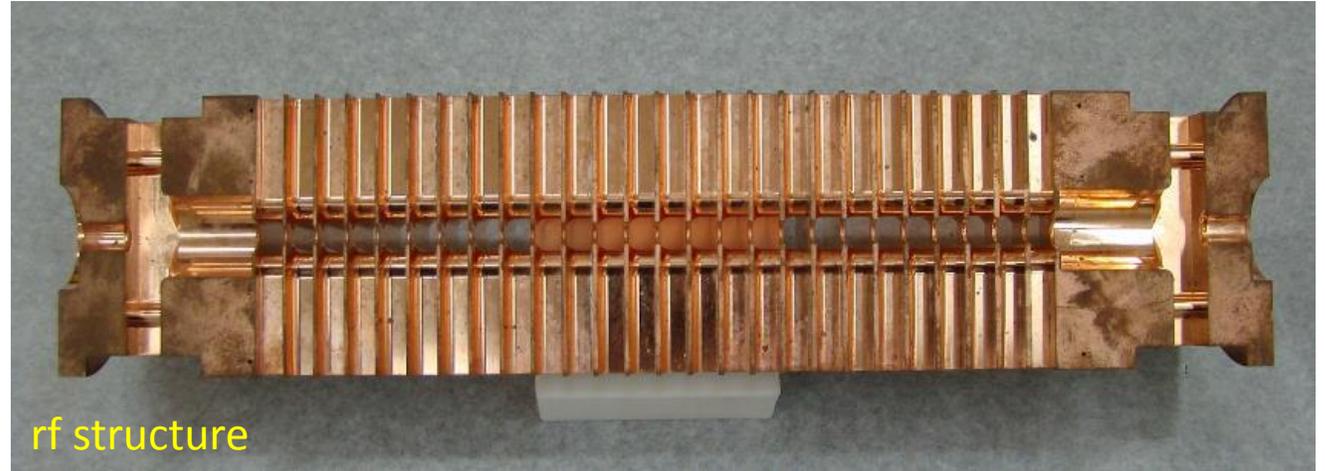
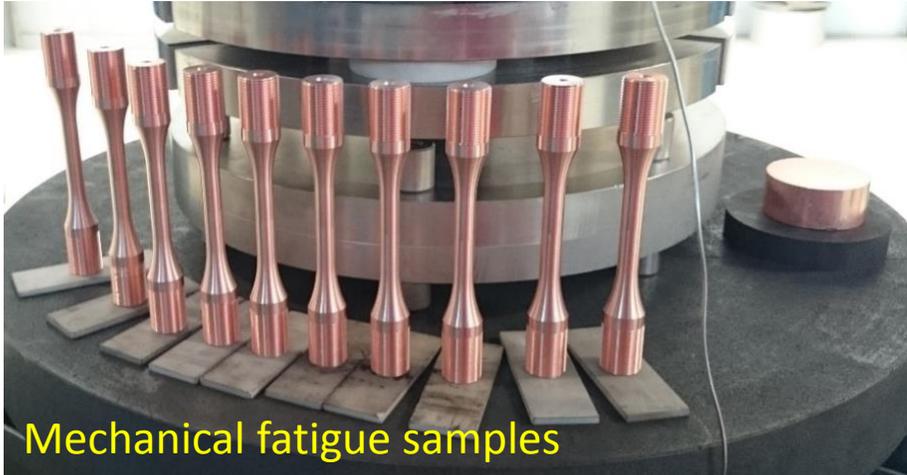


vs. number of pulses

Interpretation – conditioning proceeds as the number of pulses *not* the number of breakdowns. This implies a steady modification of the structure for each pulse.



vs. number of Breakdowns

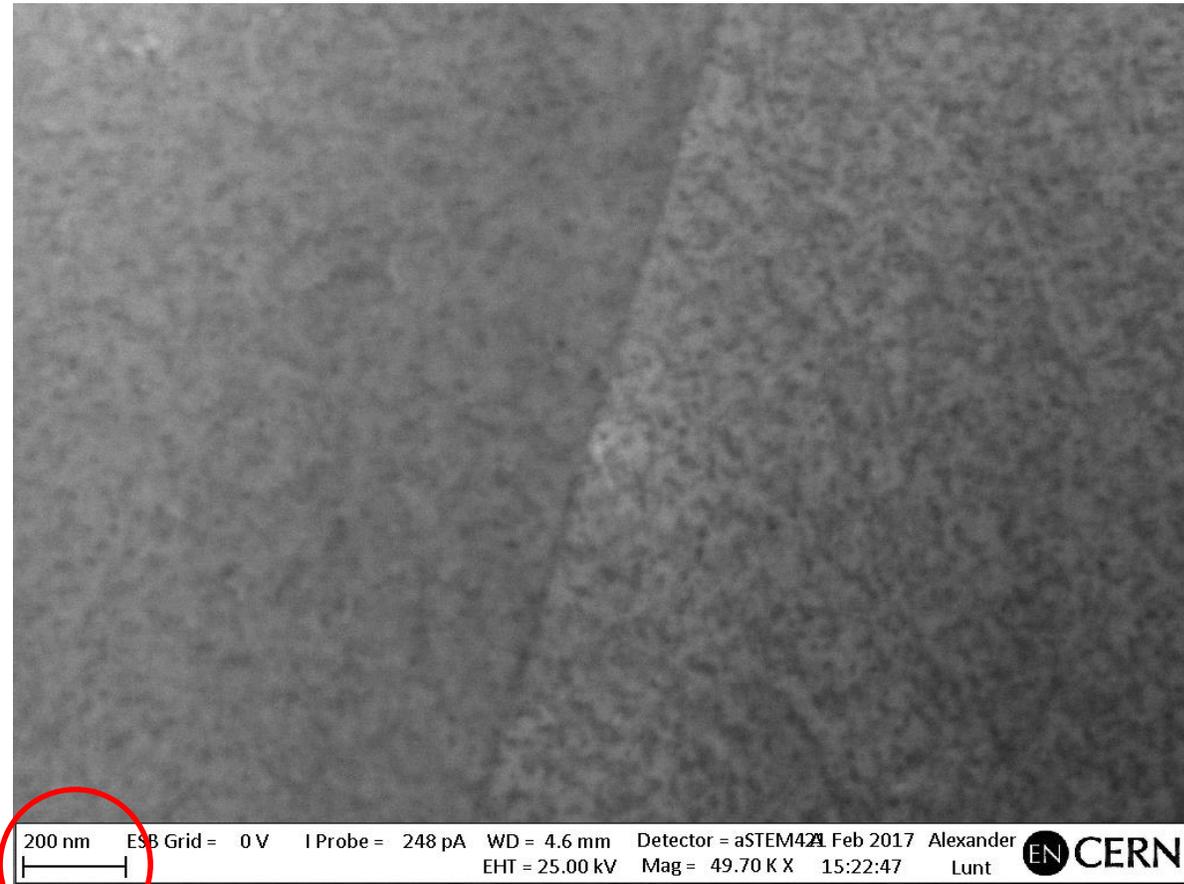


Experiment:

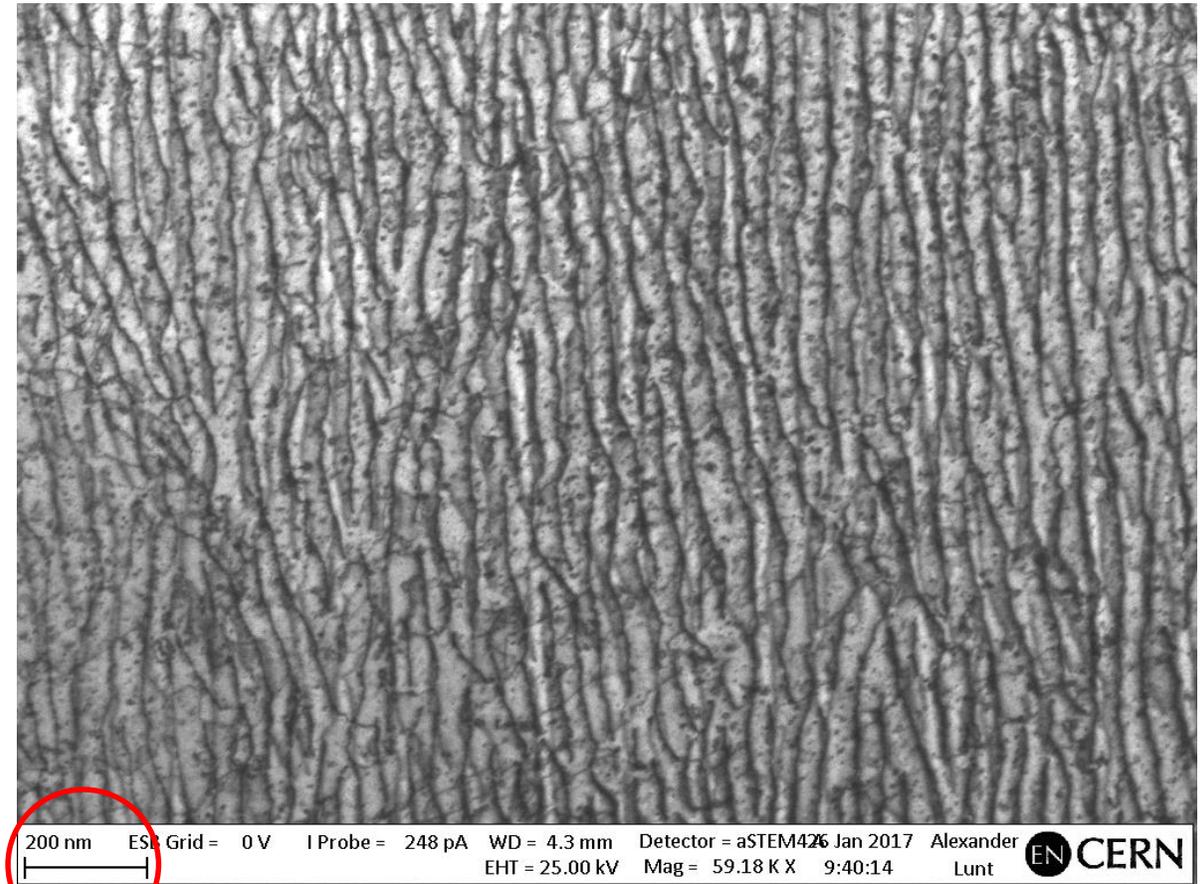
1. Build **rf structure**, standard procedure with 1040 °C bonding, and **mechanical sample** with same heat treatment.
2. Condition rf structure and fatigue mechanical sample.
3. Compare material state before/after/between using advanced microscopy techniques: FIB cutting lamella and image using STEM and TEM.



Mechanical fatigue – STEM images



After heat treatment



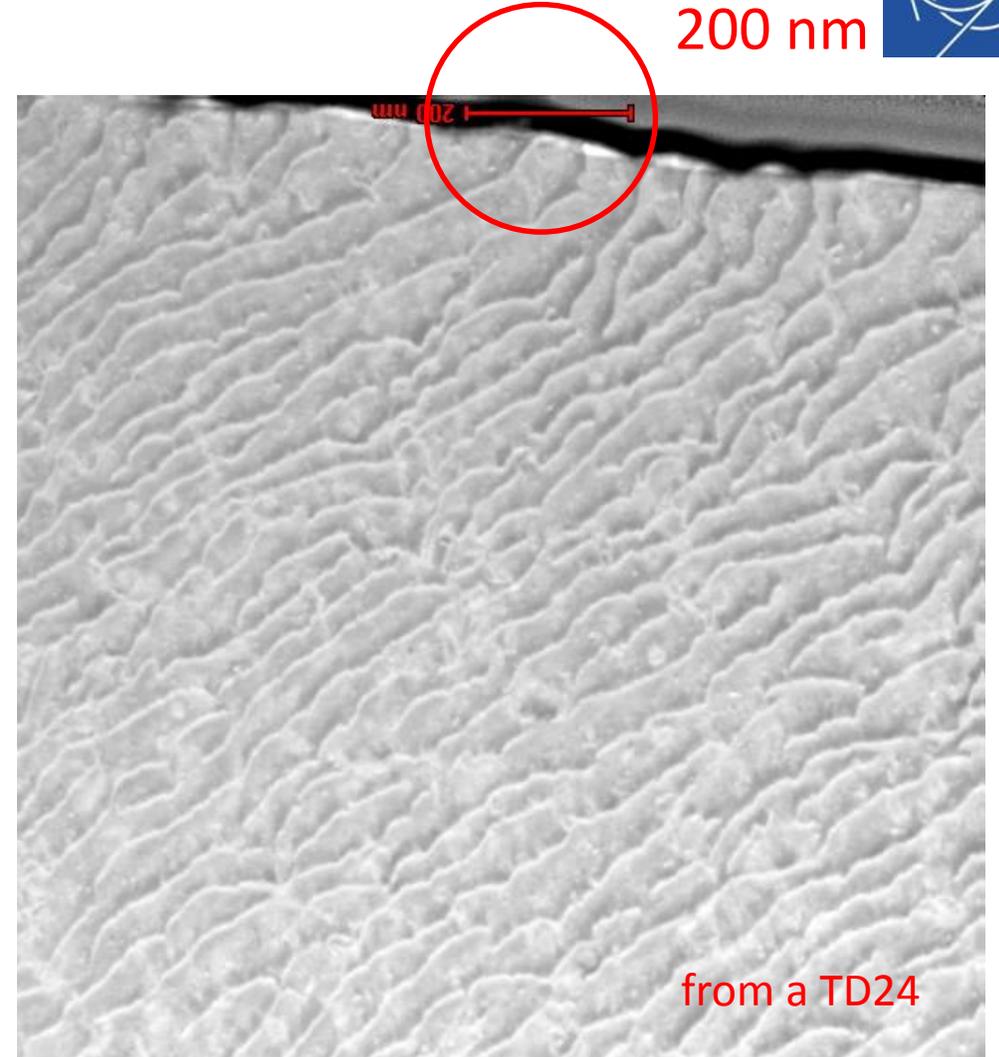
200 nm

After mechanical fatigue

Formation of dislocation patterns characteristic of hardening.



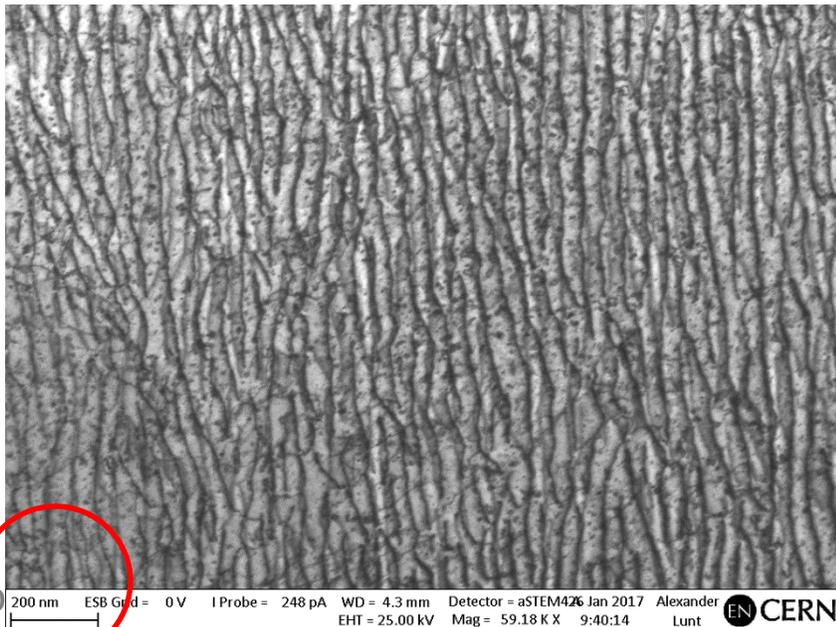
Comparison of mechanical and rf samples



200 nm

from a TD24

After rf conditioning, high E field region – TEM image





Interpretation



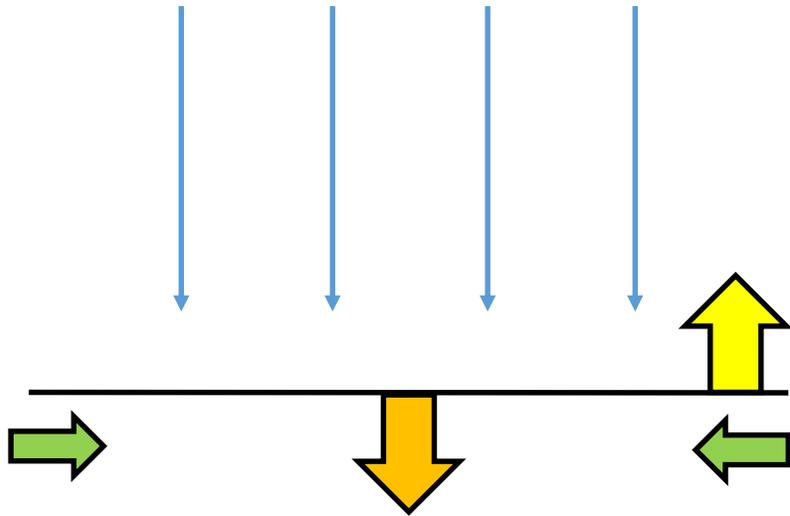
RF operation at high fields **produces dislocation patterns similar to fatigue** implying:

- A hardening process occurs during conditioning,
- Dislocation dynamics, formation and movement, are central to high-gradient behaviour.

Some numbers:

- Electric field stress is $\sigma = \frac{1}{2} \epsilon_0 E^2$ so for 250 MV/m surface field, 270 kPa – for perfect flat surface.
- The onset of plastic behaviour in Cu is of the order of kPa, so well above already at 100 MV/m surface field.
- Speed of sound in copper is .38 mm/100 ns, so bulk phenomenon.

Applied external electric field



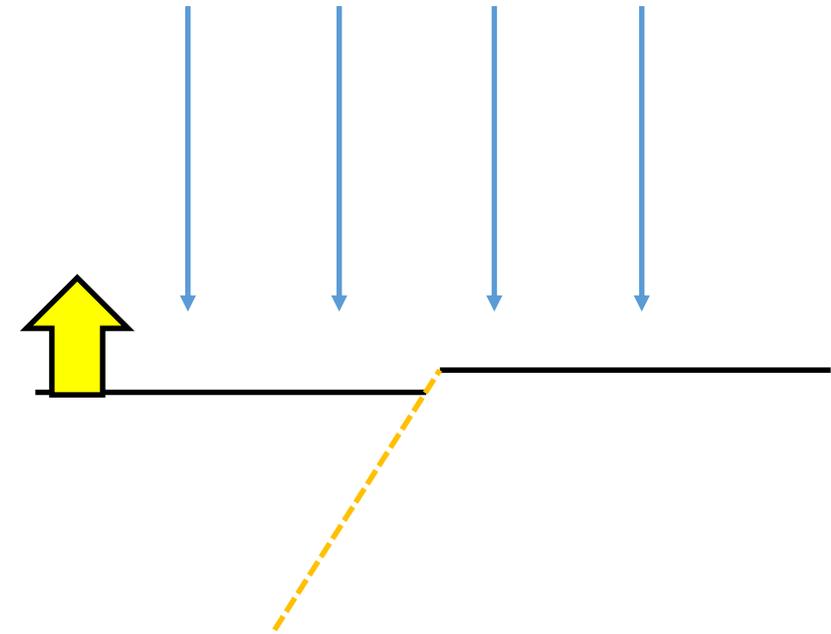
(Direct magnetic force and pulsed surface heating can be treated in same way)

- Tensile stress induces plastic behaviour, i.e. creates dislocations.
- Dislocations move to surface to reduce energy.
- Projection of dislocation on surface in **nucleation point** for continuation of breakdown process, last section and Flyura's presentation.

Vacuum

Tensile force

Copper





The mathematics behind dislocation dynamics

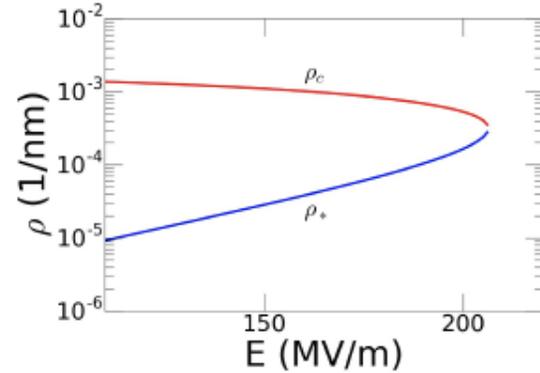


Describing mobile dislocation population evolution:

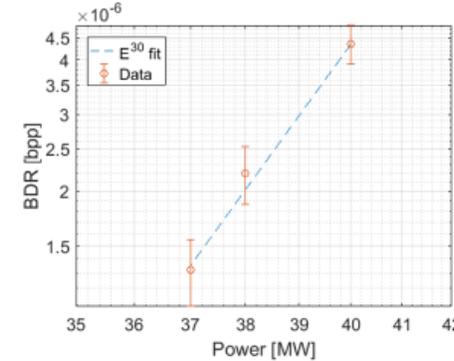
$$\dot{\rho}^+ = \frac{25\kappa C_t}{G^2 b} (\rho + c) \sigma^2 e^{-\frac{E_a - \Omega \sigma}{k_B T}}$$

$$\dot{\rho}^- = \frac{50\xi C_t}{G} \sigma \rho (c + \rho)$$

$$\sigma = \beta \epsilon_0 E^2 / 2 + ZG b \rho$$



BDR dependence



Data taken in XBox-2 with TD26CC structure, T. Lucas

CAS on Future Colliders, 4 and 5 March 2018

Regularly observed dependence:

$$BDR \propto E^{30} \tau^5$$

Physical model based on defect formation

$$BDR \propto e^{-\frac{E^f + \epsilon_0 E^2 \Delta V}{k_B T}}$$

$$E^f = 0.8 \text{ eV}$$

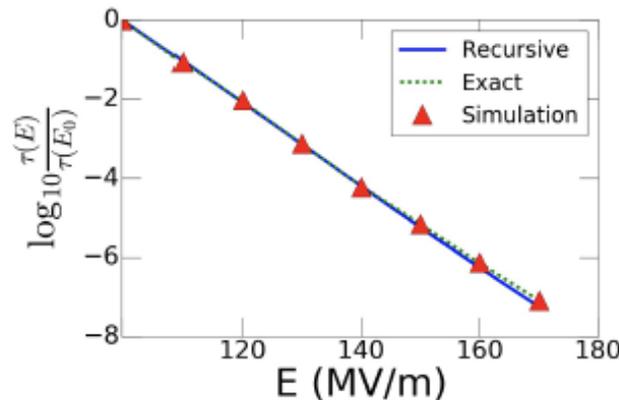
$$\Delta V = 0.8 \times 10^{-24} \text{ m}^3$$

K. Nordlund, F. Djurabekova, Defect model for the dependence of breakdown rate on external electric fields, Phys. Rev. ST Accel. Beams 15, 071002 (2012)

Walter Wuensch, CERN

Leads to an exponential decay:

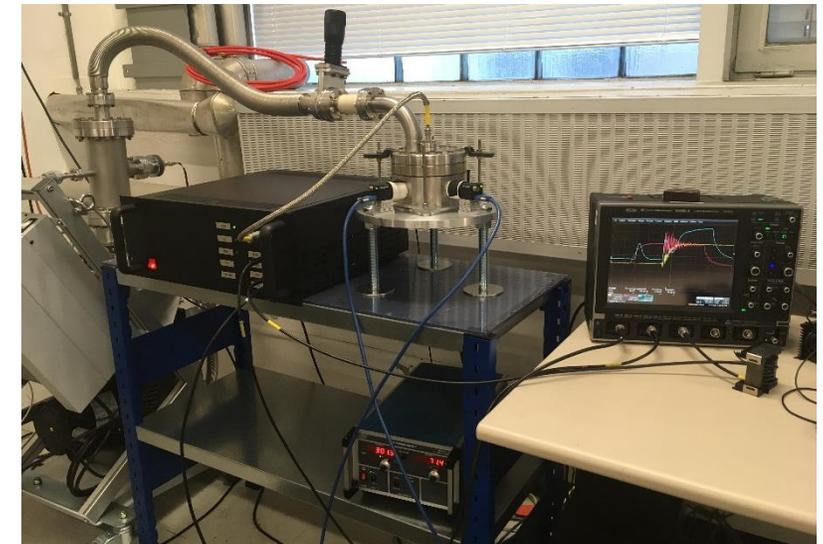
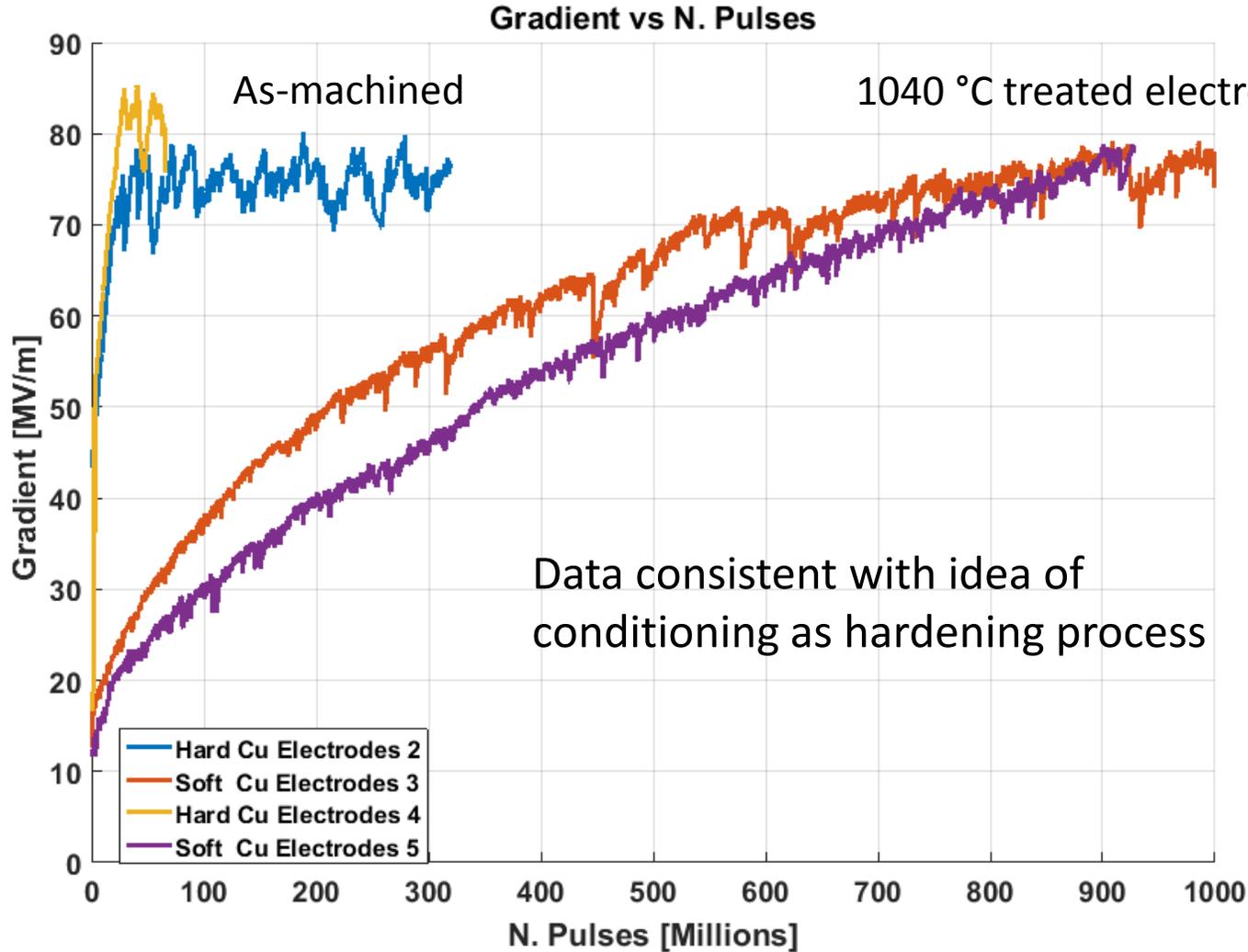
Y. Ashkenazy and E. Engelberg



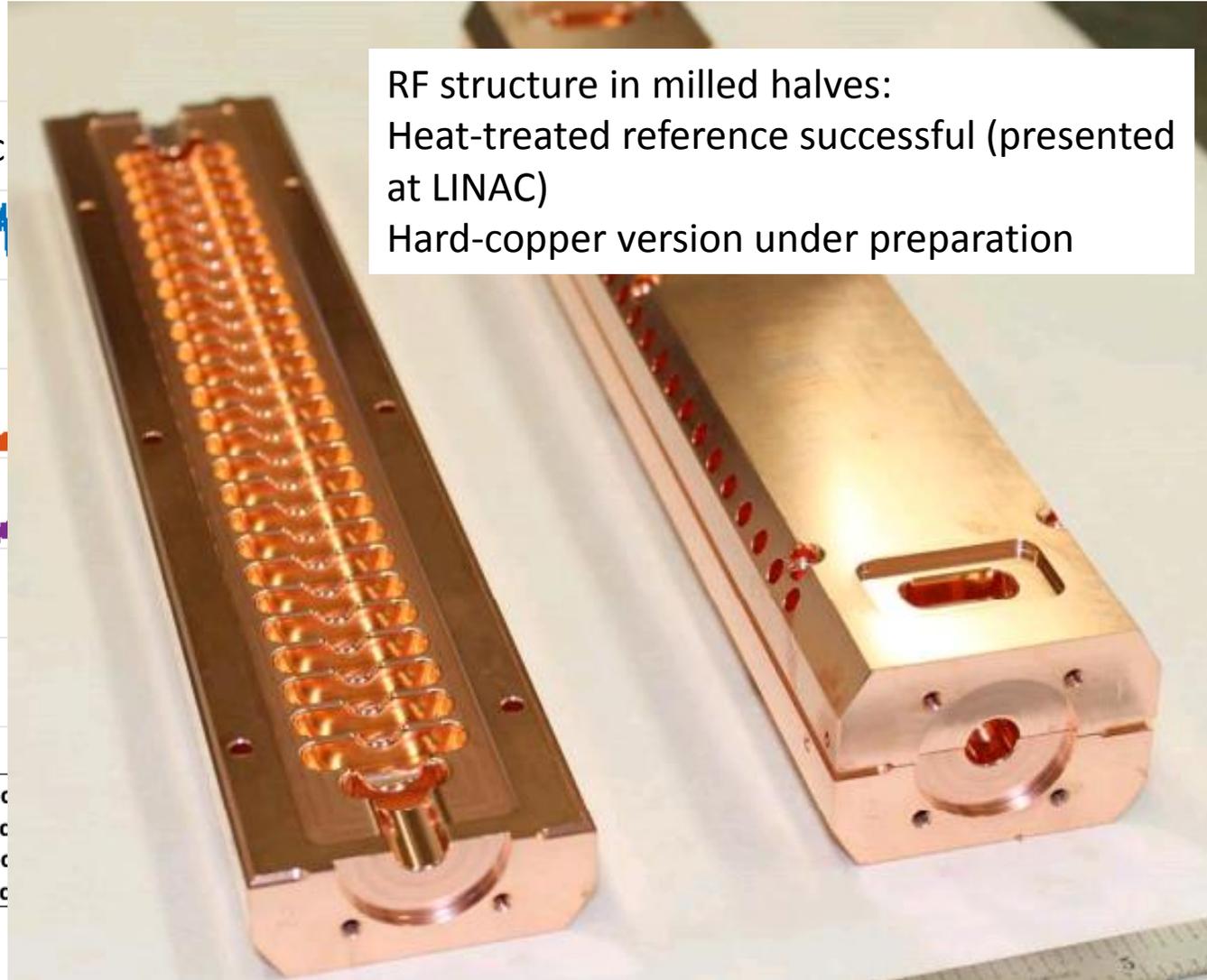
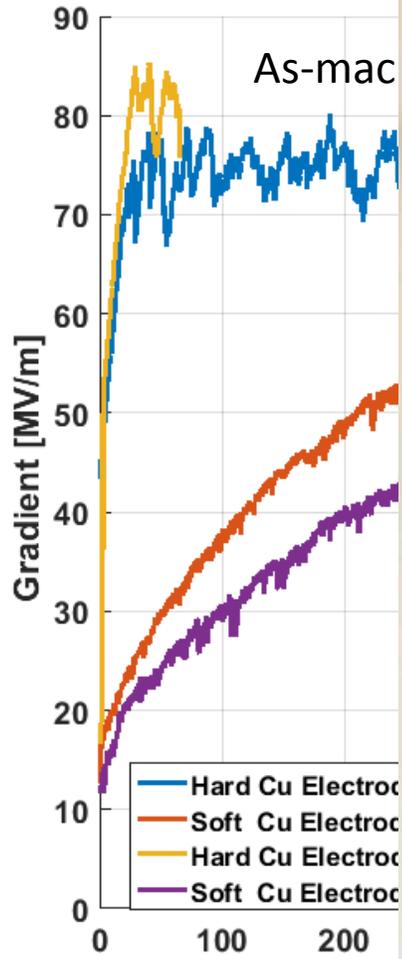
$$\tau \sim e^{-\gamma \frac{E}{E_0}}$$

Accepted for publication in PRL

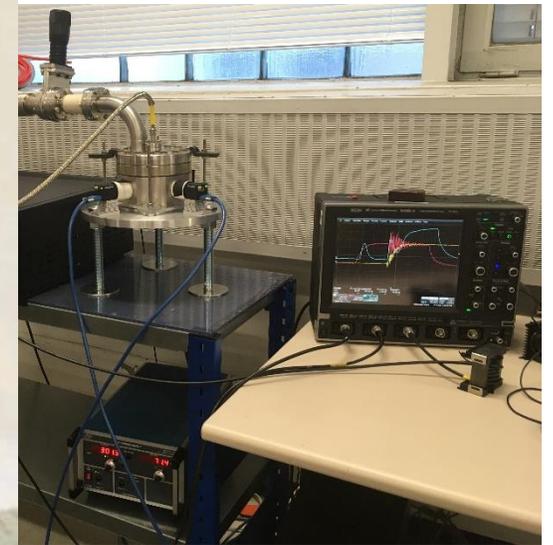
Hard vs. soft copper in pulsed dc system



Hard vs. soft copper in pulsed dc system



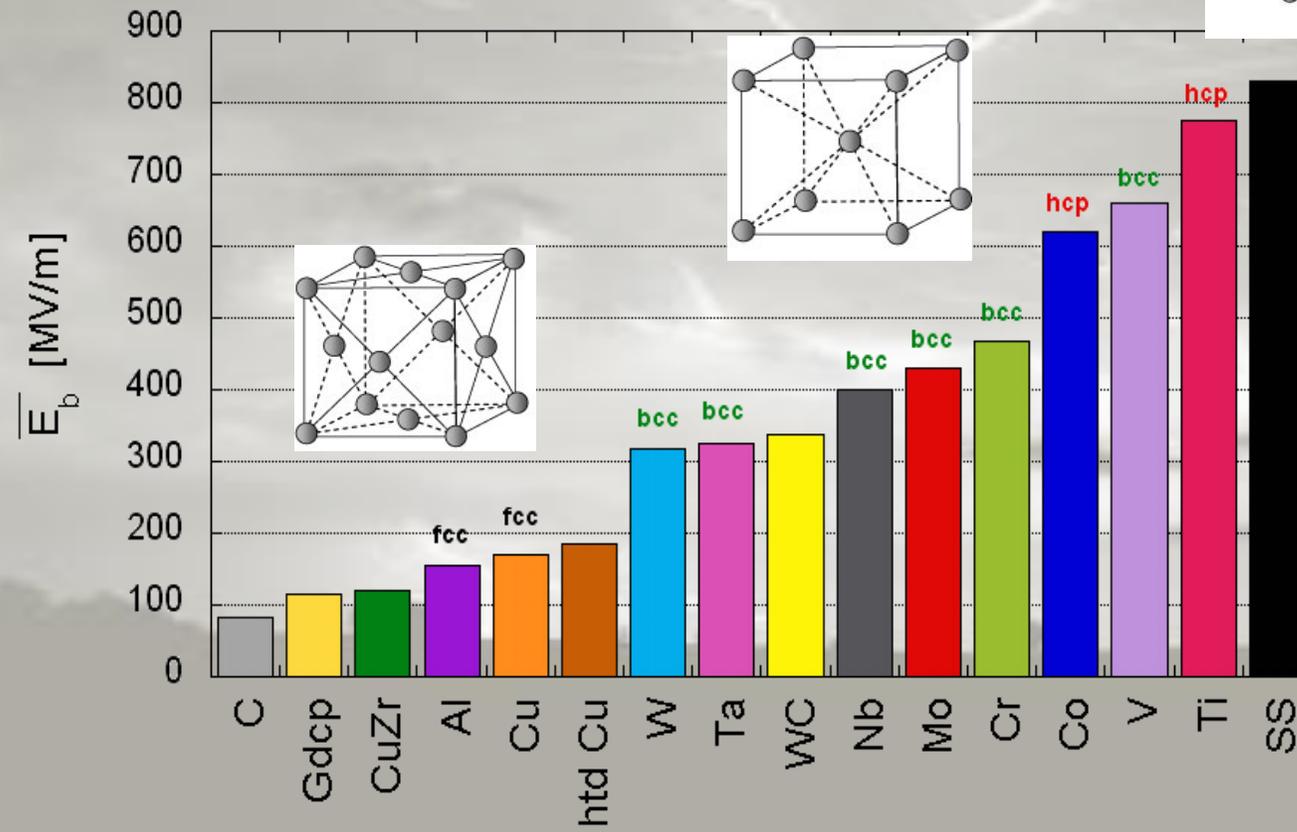
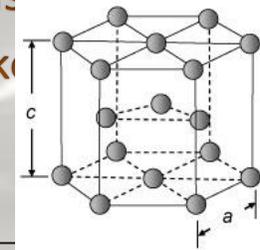
RF structure in milled halves:
 Heat-treated reference successful (presented at LINAC)
 Hard-copper version under preparation





What are the field emitters? Why do we look for dislocations?

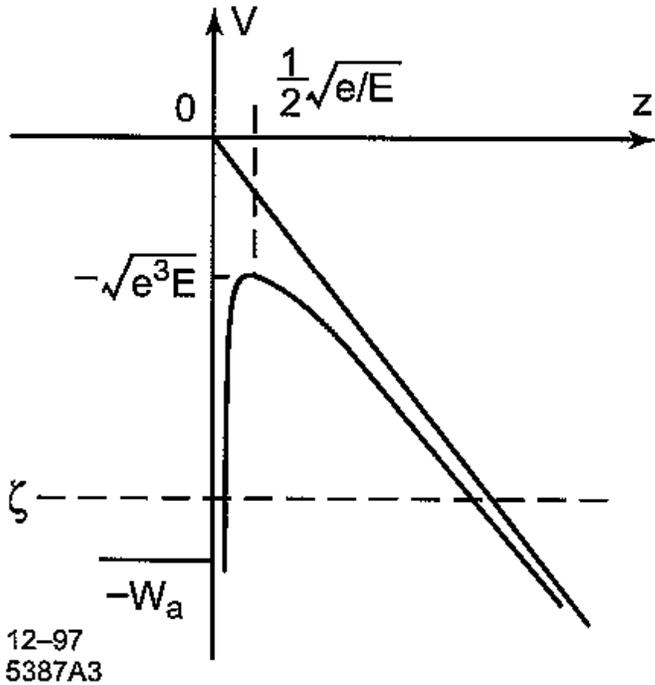
- The dislocation motion is strongly bound to the atomic structure of metals. In FCC (face-centered cubic) the dislocation are the most mobile and HCP (hexagonal close-packed) are the hardest for dislocation mobility.



A. Descoeur, F. Djurabekova, and K. Nordlund, DC Breakdown experiments with cobalt electrodes, CLIC-Note 875, 1 (2010).

Field emission

- A sufficiently strong surface electric field causes electrons to be emitted from a metal surface. This is described by the Fowler-Nordheim equation.
- Functional form fits experiments perfectly, but there is an ever present need for a correction factor β , which is typically 30, and can be much higher. Attributed variously to small geometric features, locally lower work function and contaminants.

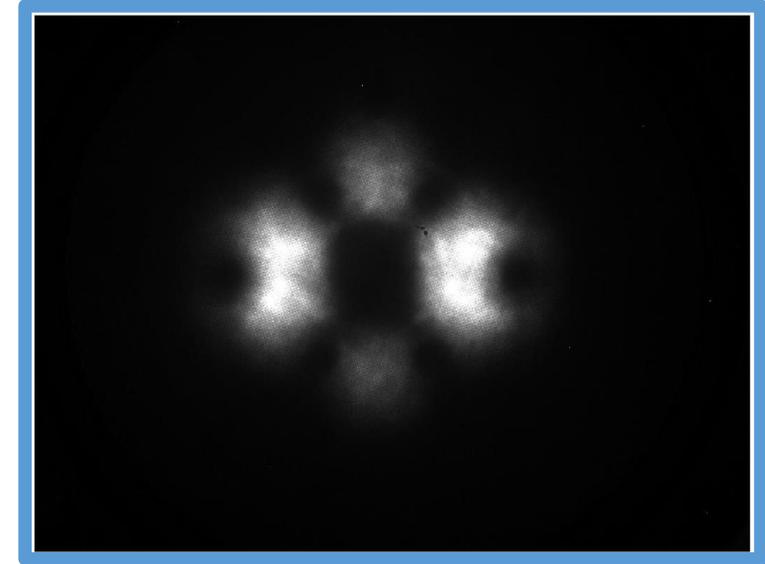
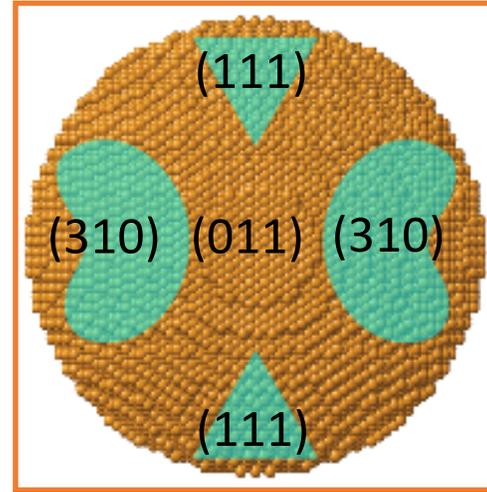
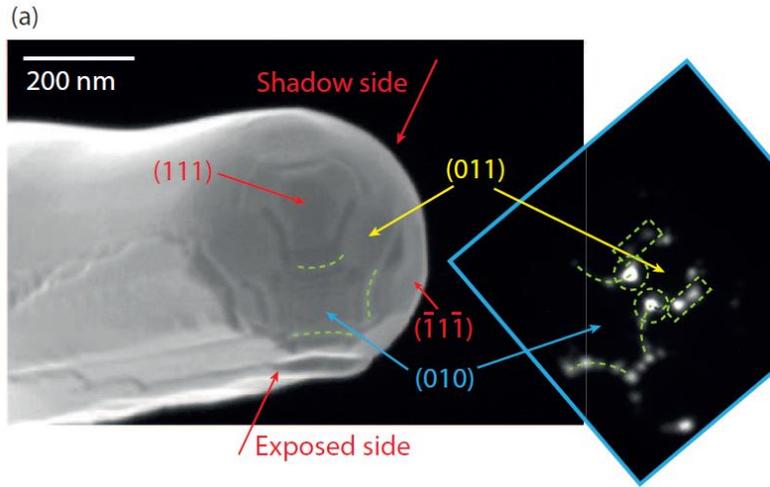


$$I = A_e \frac{1.54 \times 10^6 \beta^2 E^2}{\phi} e^{10.41 \phi^{-1/2}} \times e^{-6.53 \times 10^3 \times \phi^{3/2} / \beta E}$$

$$= \zeta E^2 e^{-6.53 \times 10^3 \phi^{3/2} / \beta E}$$

Units: $[I]=A$, $[E]=MV/m$, $[A_e]=m^2$, $[\phi]=eV$ and $[\beta]=dimensionless$

Values: $\phi = 4.5 eV$ for copper

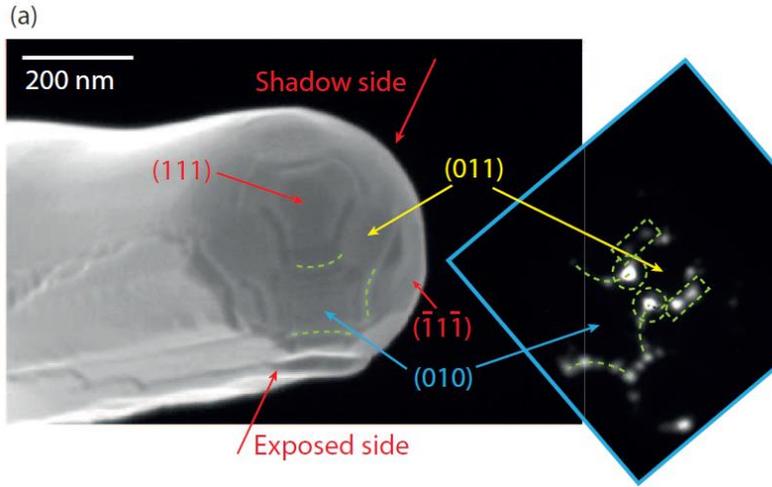


Tungsten tip used in ultra-fast electron diffraction.

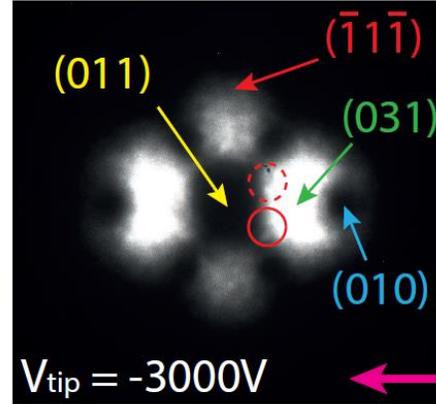
Tips deteriorate under laser pulsing but:

- Small area to uniquely identify characteristics of field emission sites
- Intense femtosecond fields opportunity to benchmark molecular dynamics and kinetic Monte Carlo codes

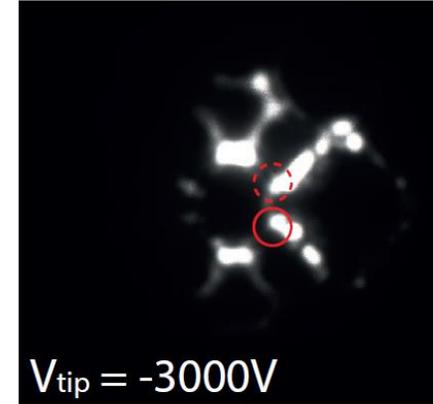
Hirofumi Yanagisawa, et. al. *Laser-induced asymmetric faceting and growth of a nano-protrusion on a tungsten tip*, APL Photonics 1, 091305 (2016); doi: 10.1063/1.4967494



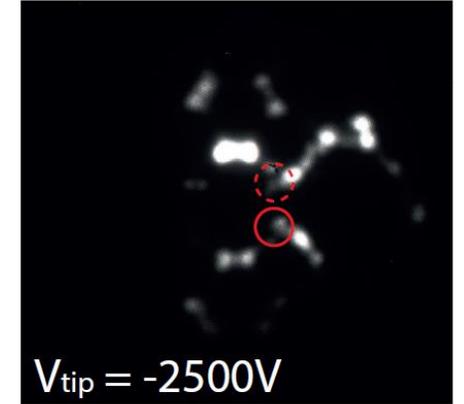
(a) 0 min



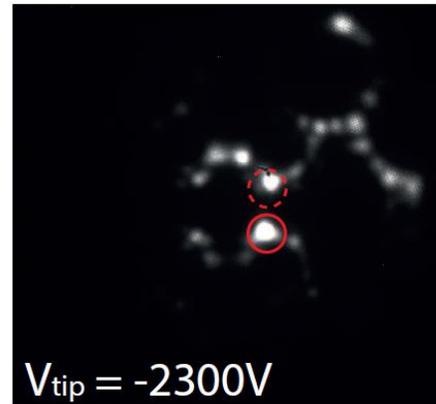
(b) 5 min



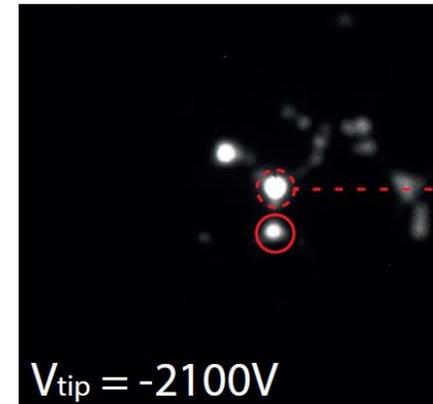
(c) 40 min



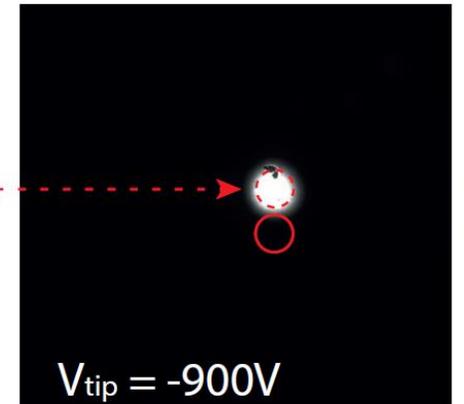
(d) 140 min



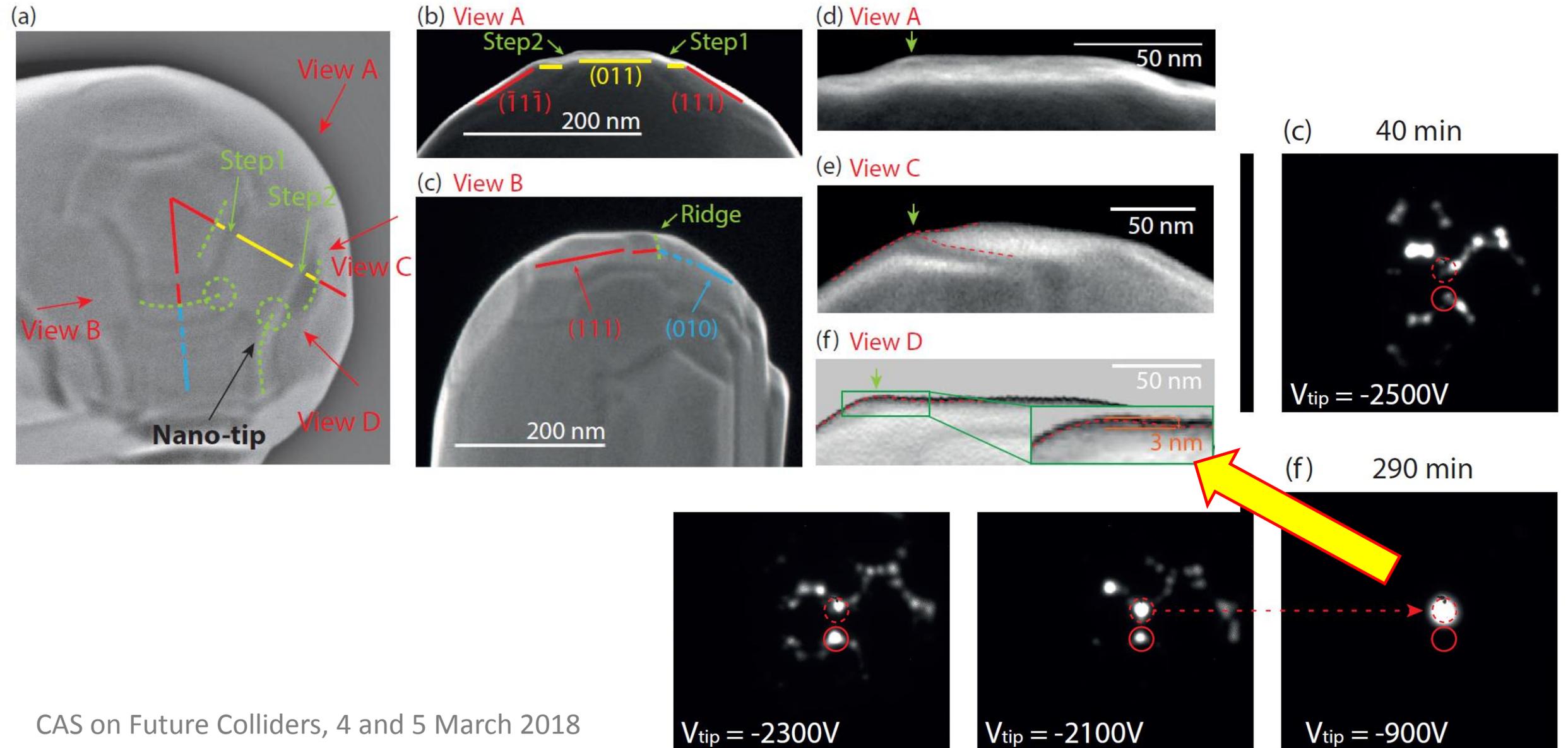
(e) 260 min



(f) 290 min



Identification of nm-sized emission site



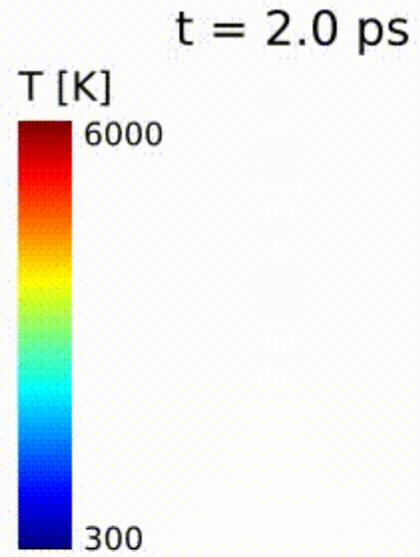
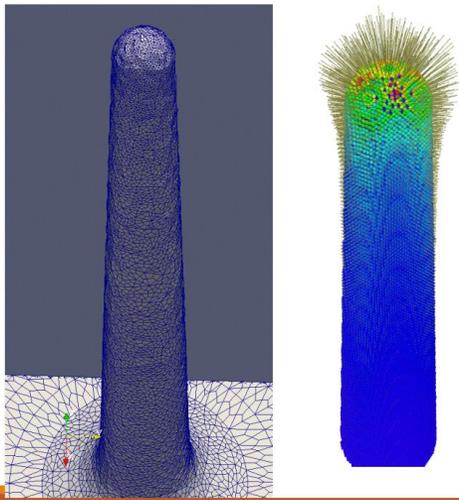
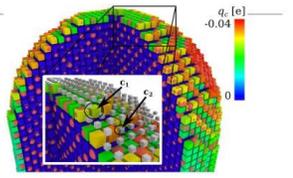
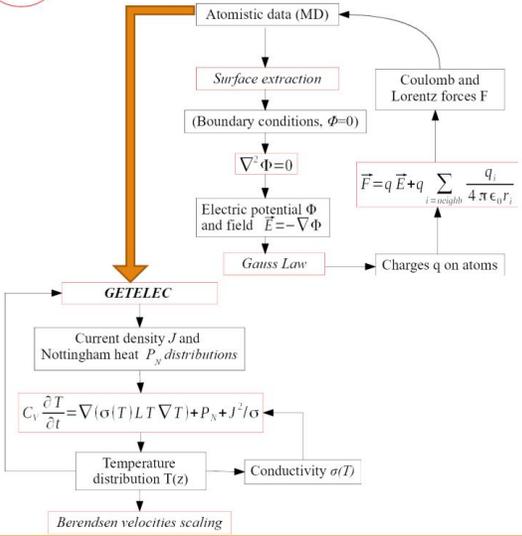


Tip evolution



Electronic+Thermal effects in MD

There are many processes which are calculated concurrently in the current implementation:

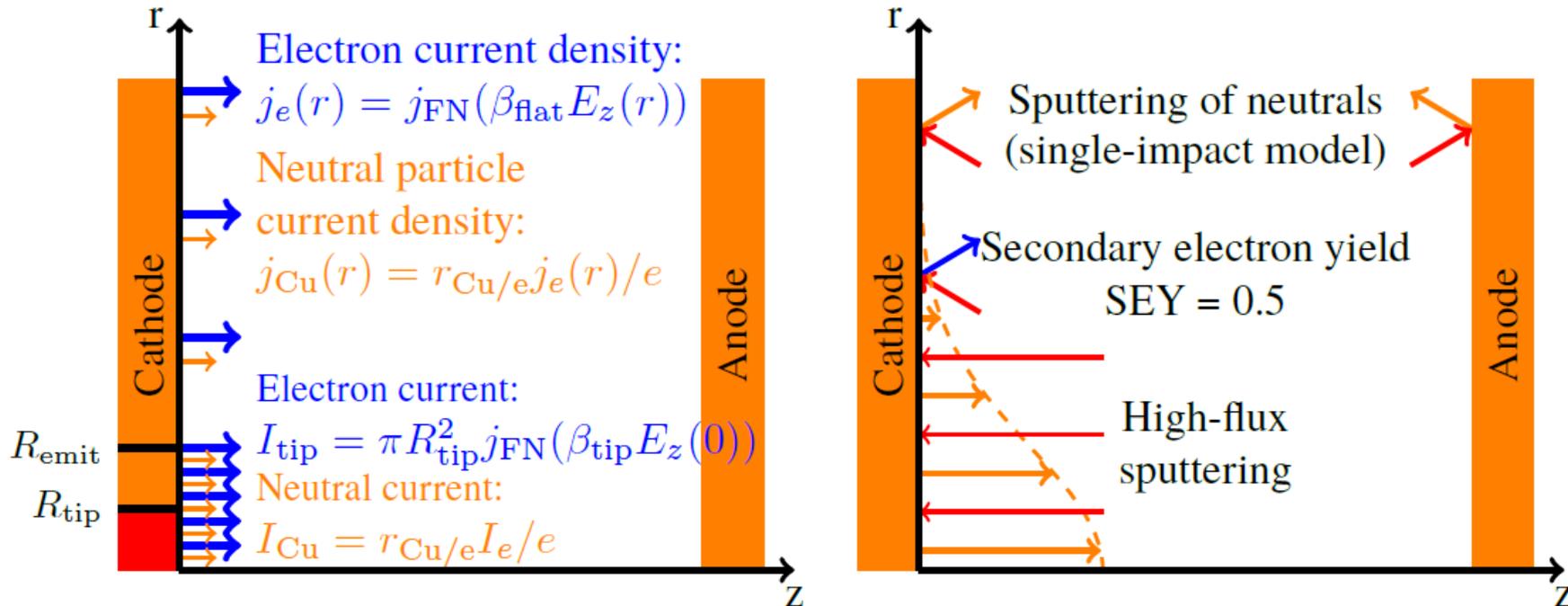




What's going on inside.

ArcPIC simulation of the onset of breakdown, starting from field emission and going through the formation of a plasma, a plasma sheath and dramatically rising emitted current.

The code is ArcPIC and simulates a 20 micron wide dc gap.

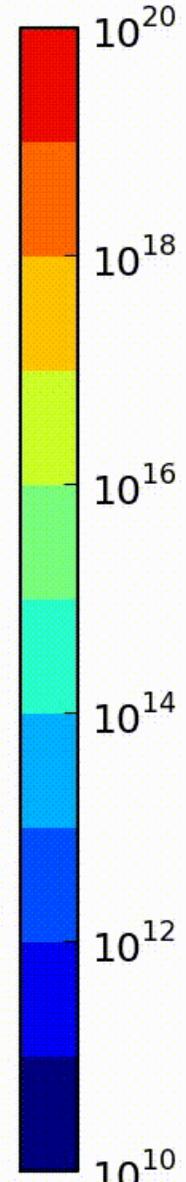
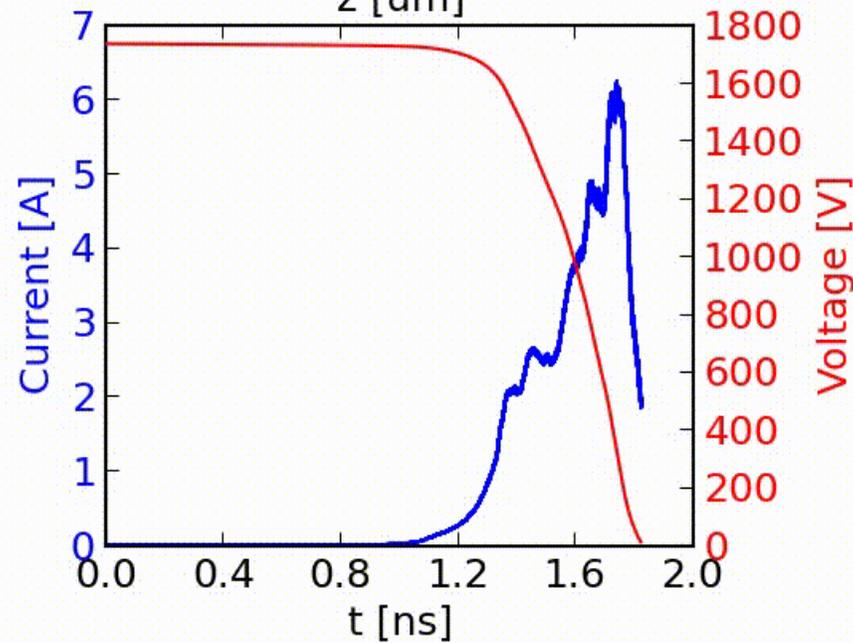
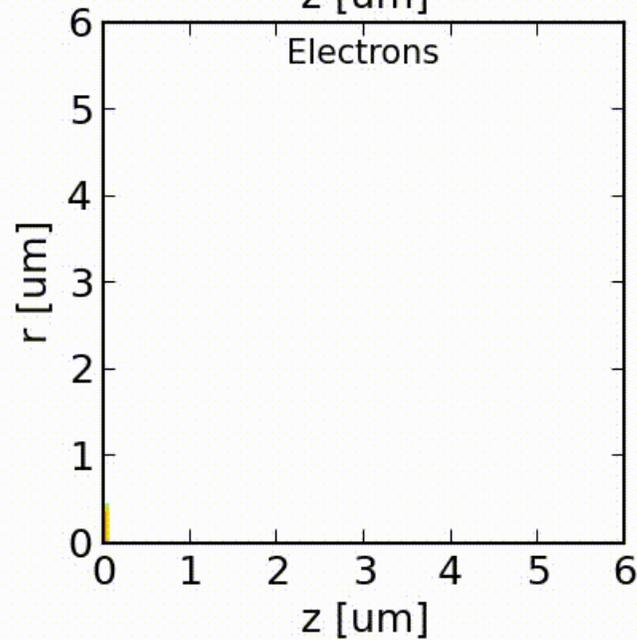
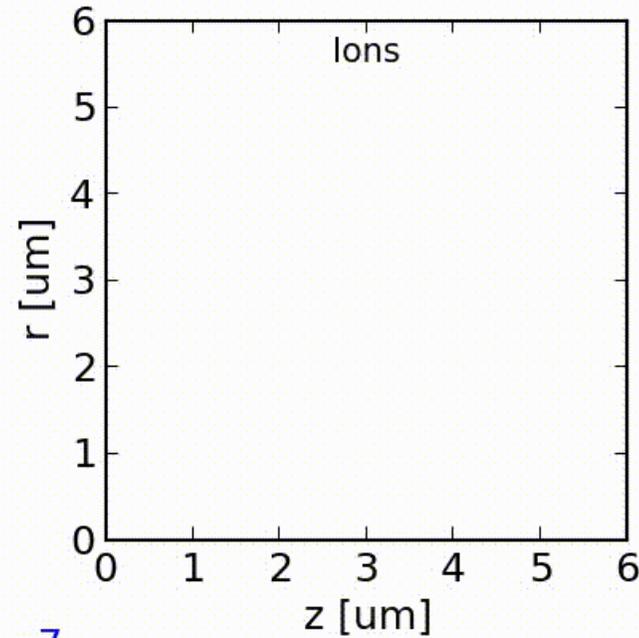
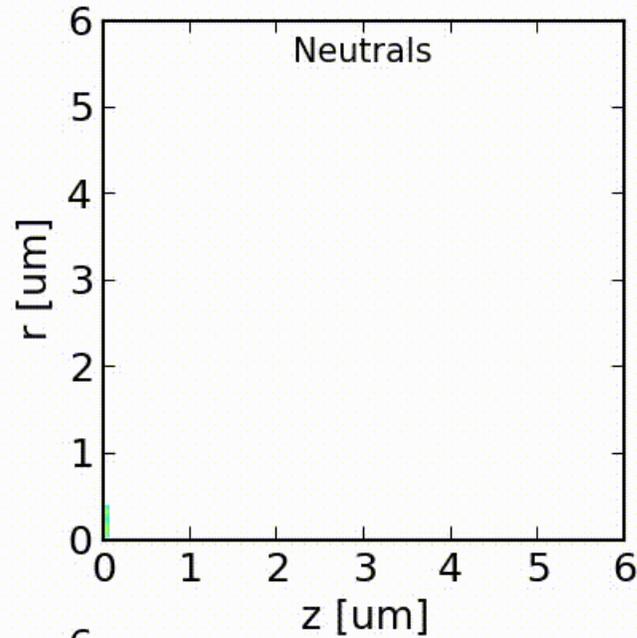


(a) Field emission and neutral evaporation.

(b) Sputtering and secondary electron yield.



Densities, time = 0.000 [ns]





Cartoon summary of the steps which lead to breakdown



An overview of the breakdown process



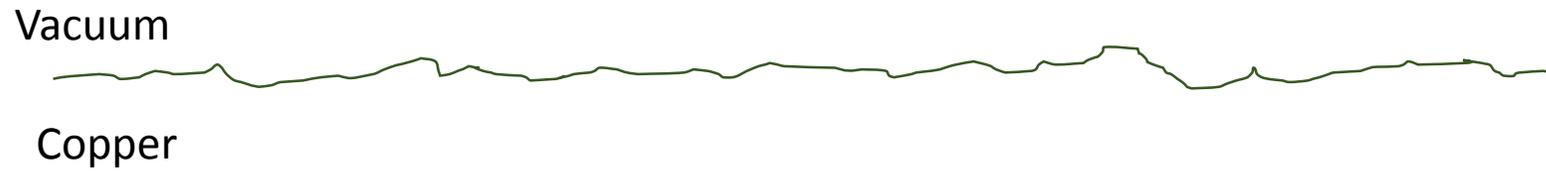
Vacuum



Copper

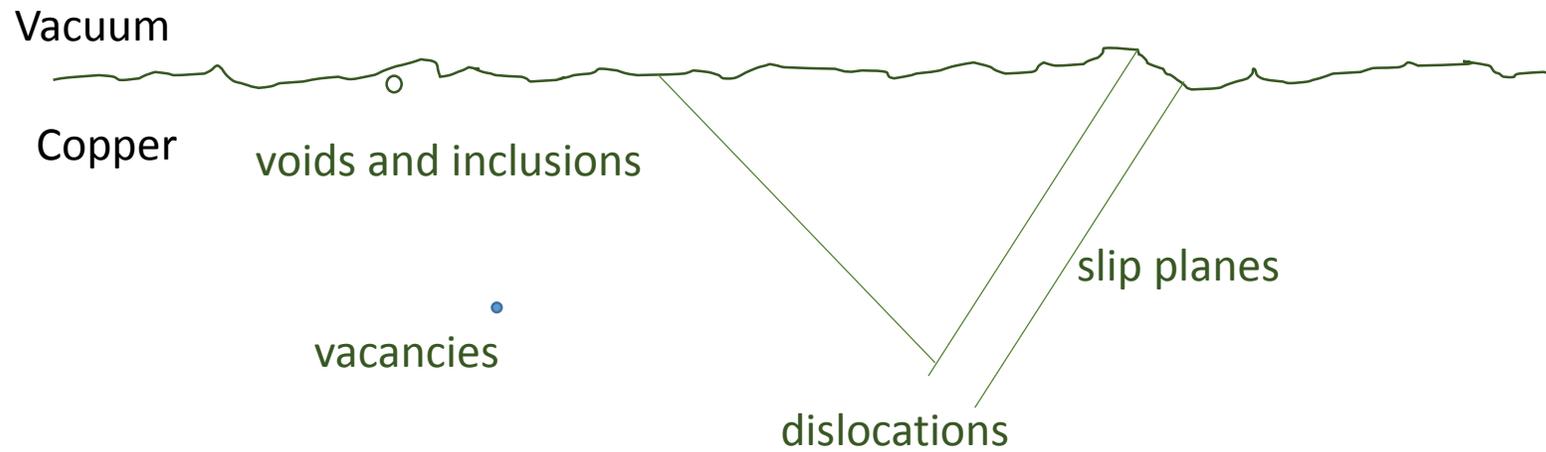


Actually real surfaces are imperfect



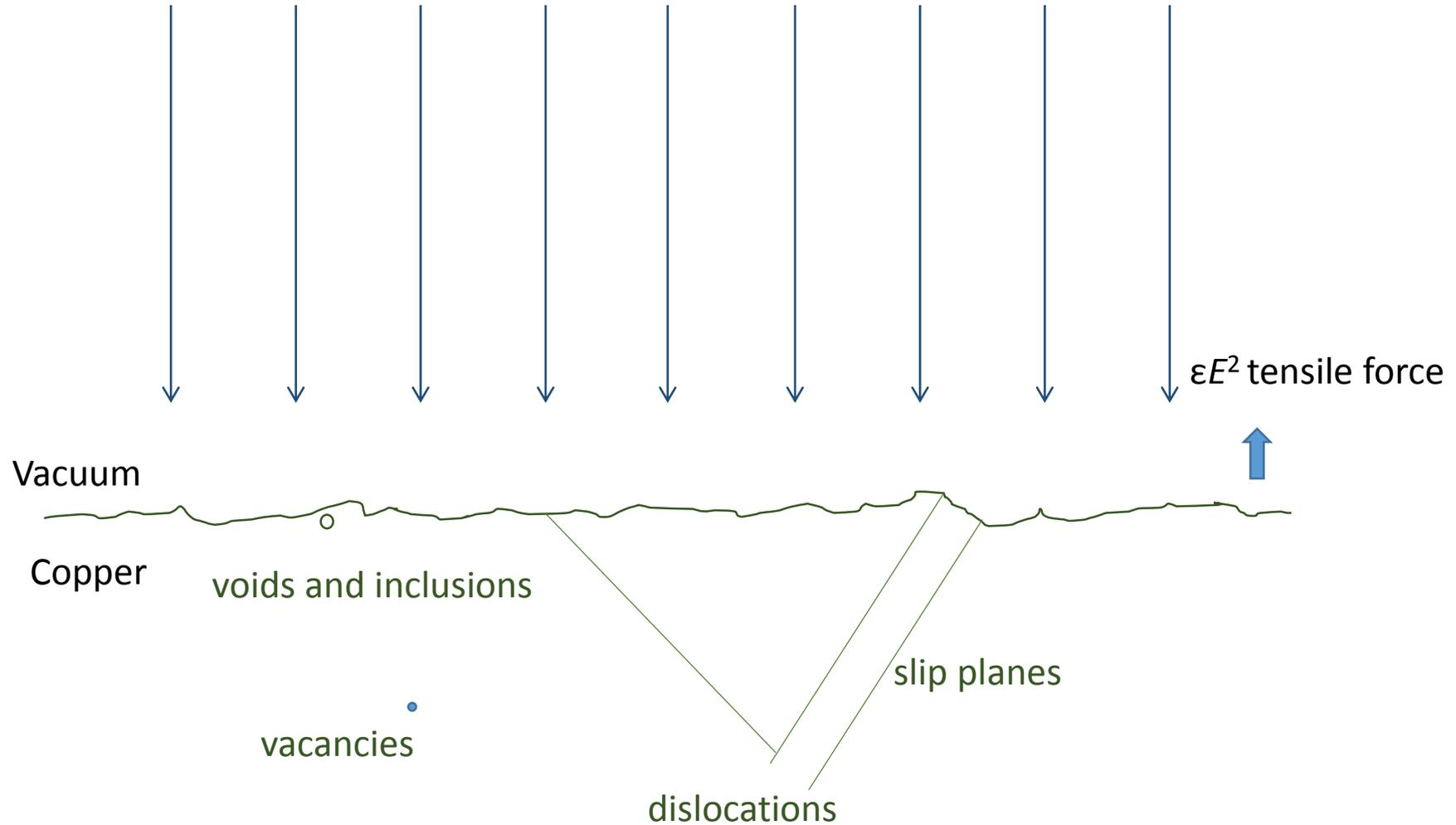


And the material below the surface isn't perfect either

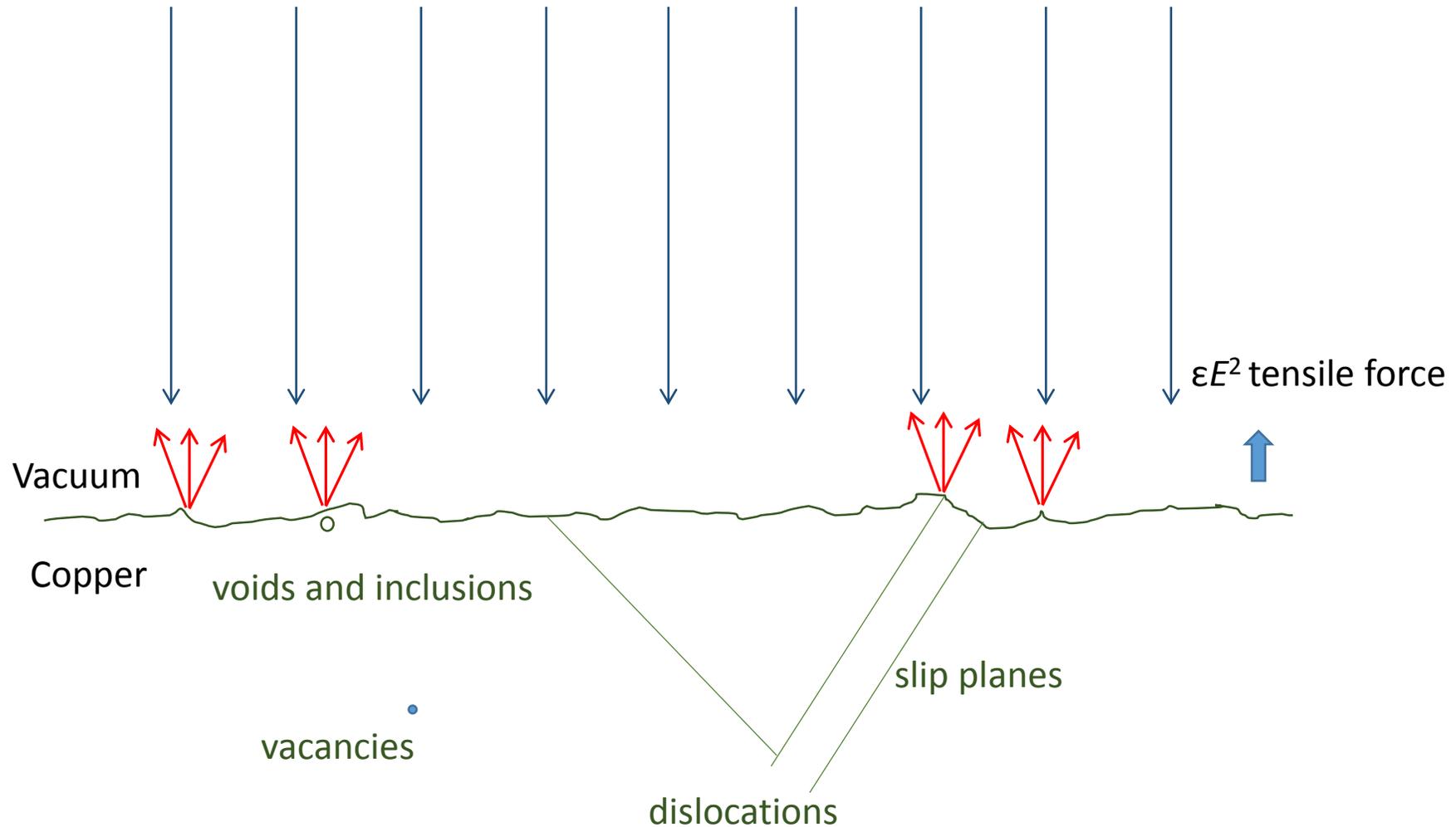




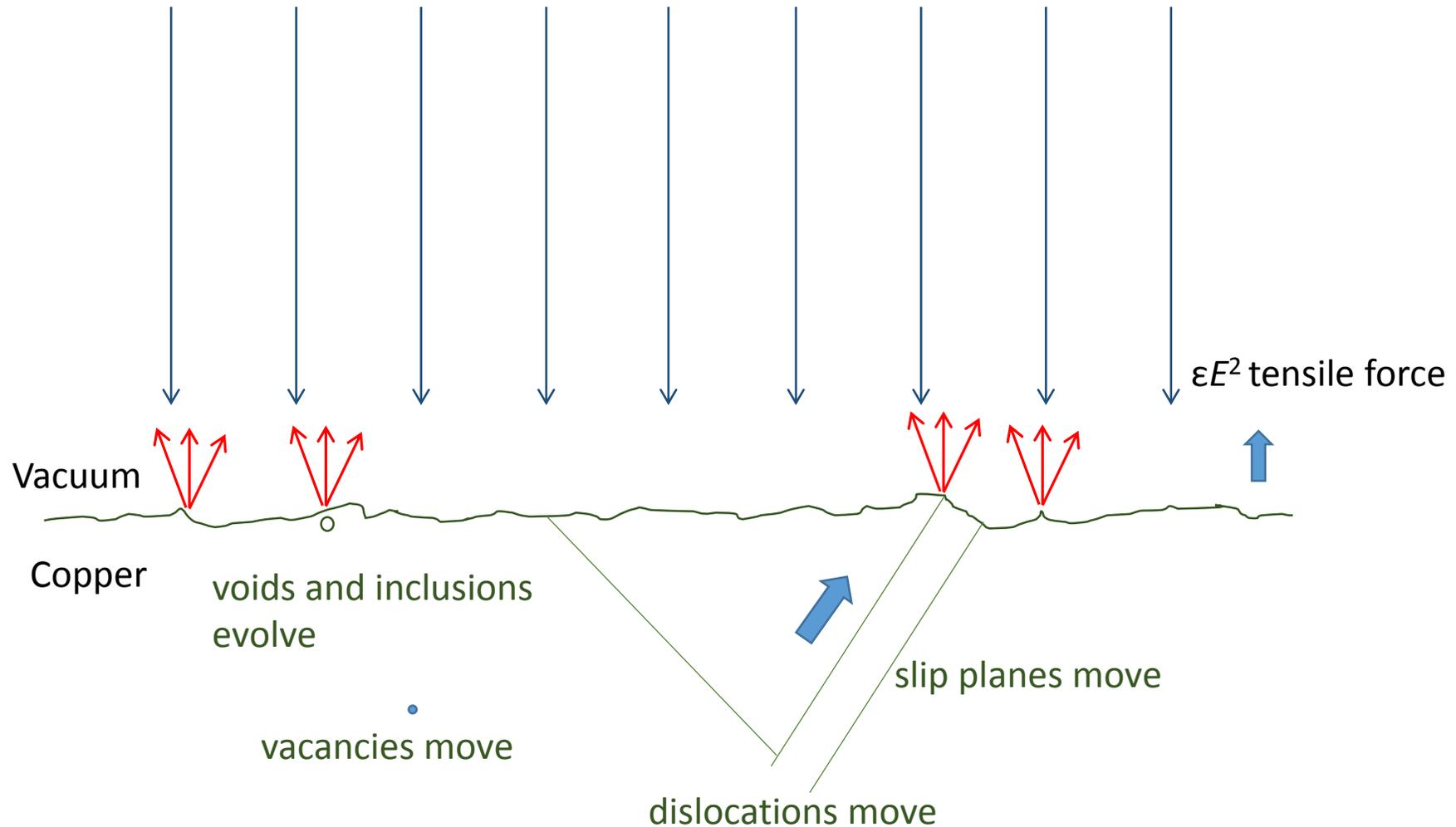
Add an external electric field, around 200 MV/m. Surface charges re-arrange themselves in fs. Surface experiences ϵE^2 tensile force.



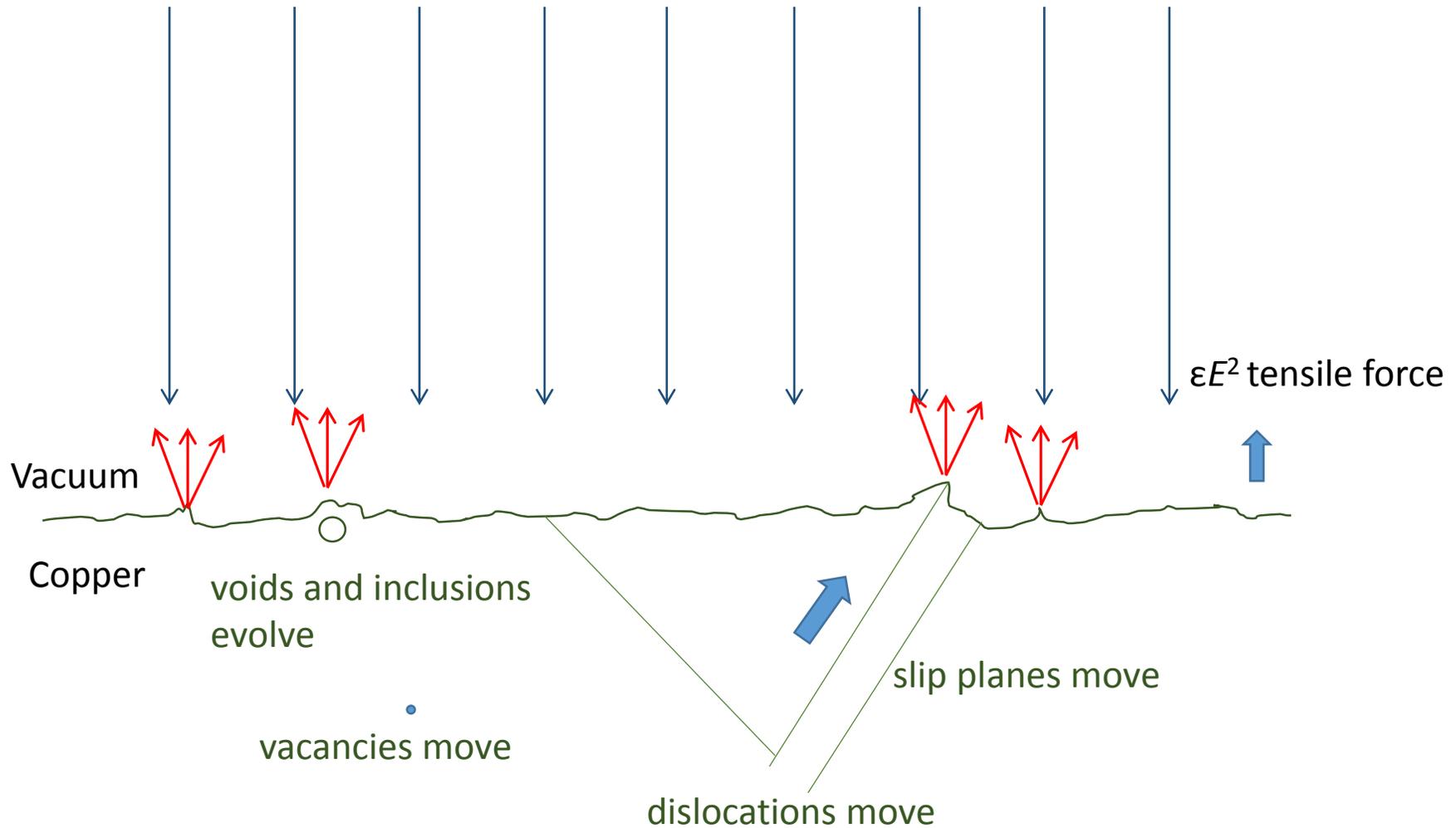
Field emission current flows from metal into vacuum (Fowler-Nordheim) from local areas ($O[10 \text{ nm}]$) of geometrical field enhancement and low local work function. There is a local field enhancement β of around 50-100. The total current from something like 0.1 mm^2 is a nanoAmp.



The external electric field causes the tensile stress and field emission current causes thermal induces stresses so the material imperfections and surface features evolve – plastic deformation.

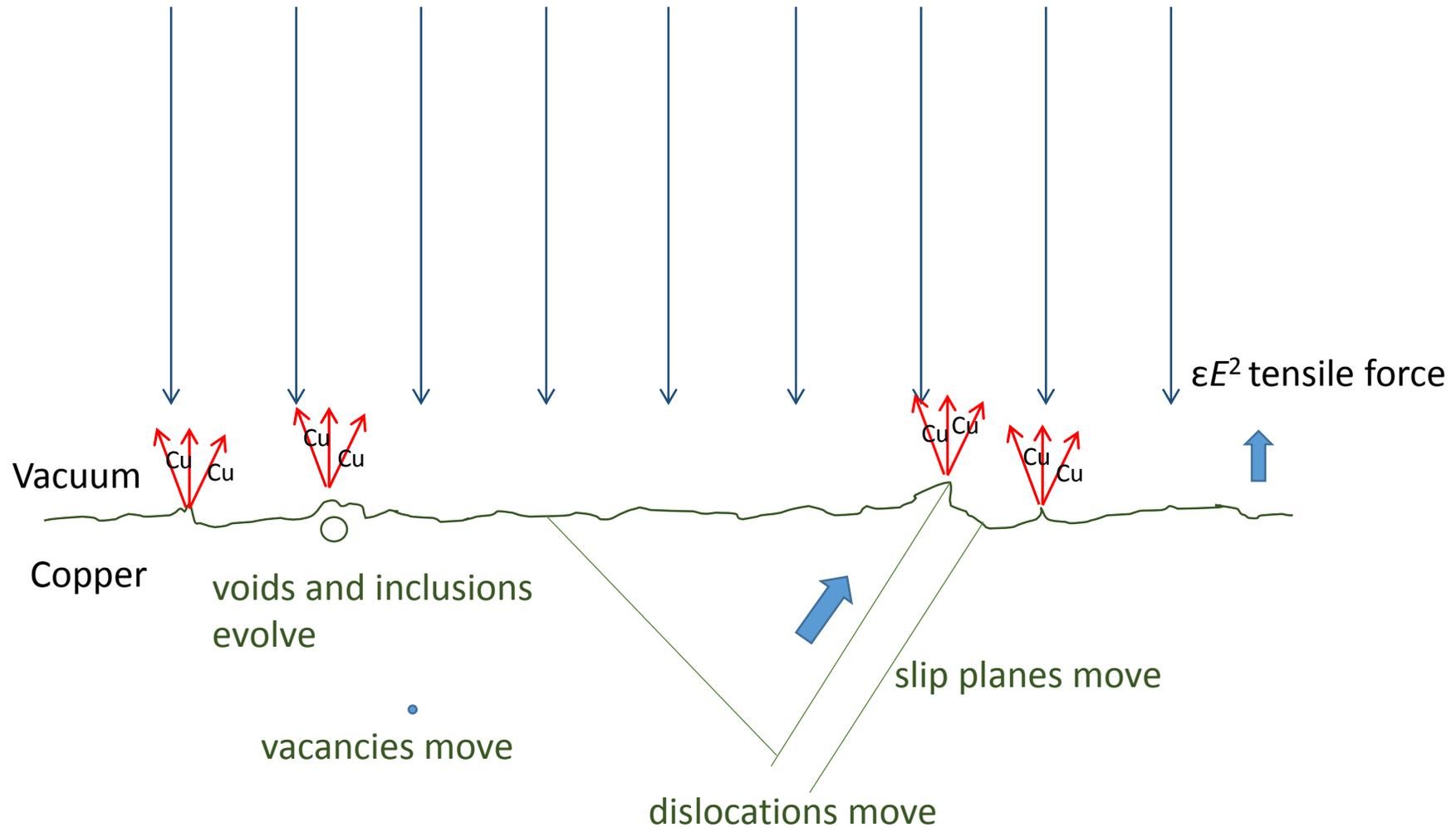


The external electric field causes the tensile stress and field emission current causes thermal induces stresses so the material imperfections and surface features evolve – plastic deformation.

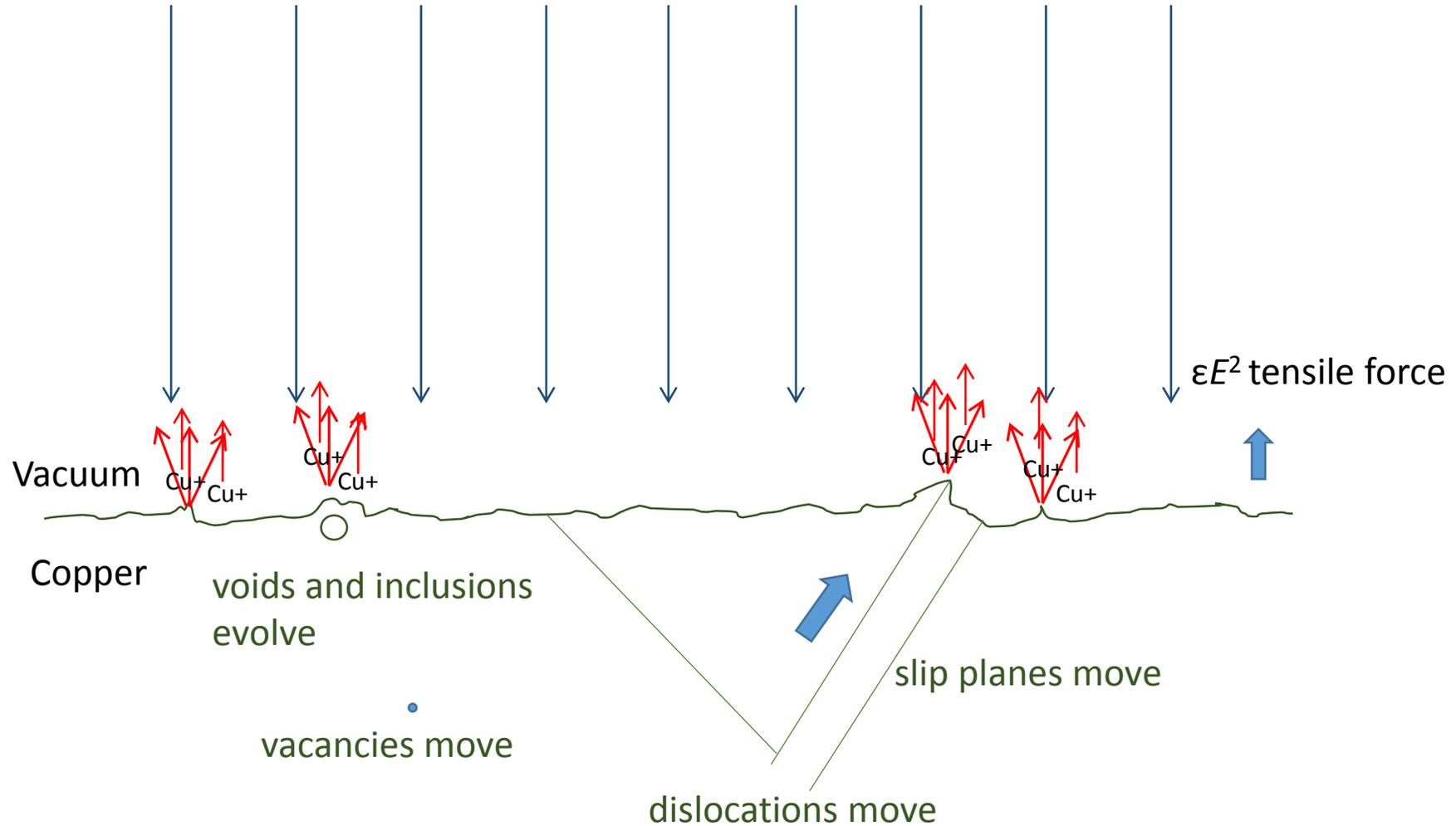




All the while, neutral copper atoms are coming off the surface field assisted evaporation.
The details of this process is process is a fundamental open question.

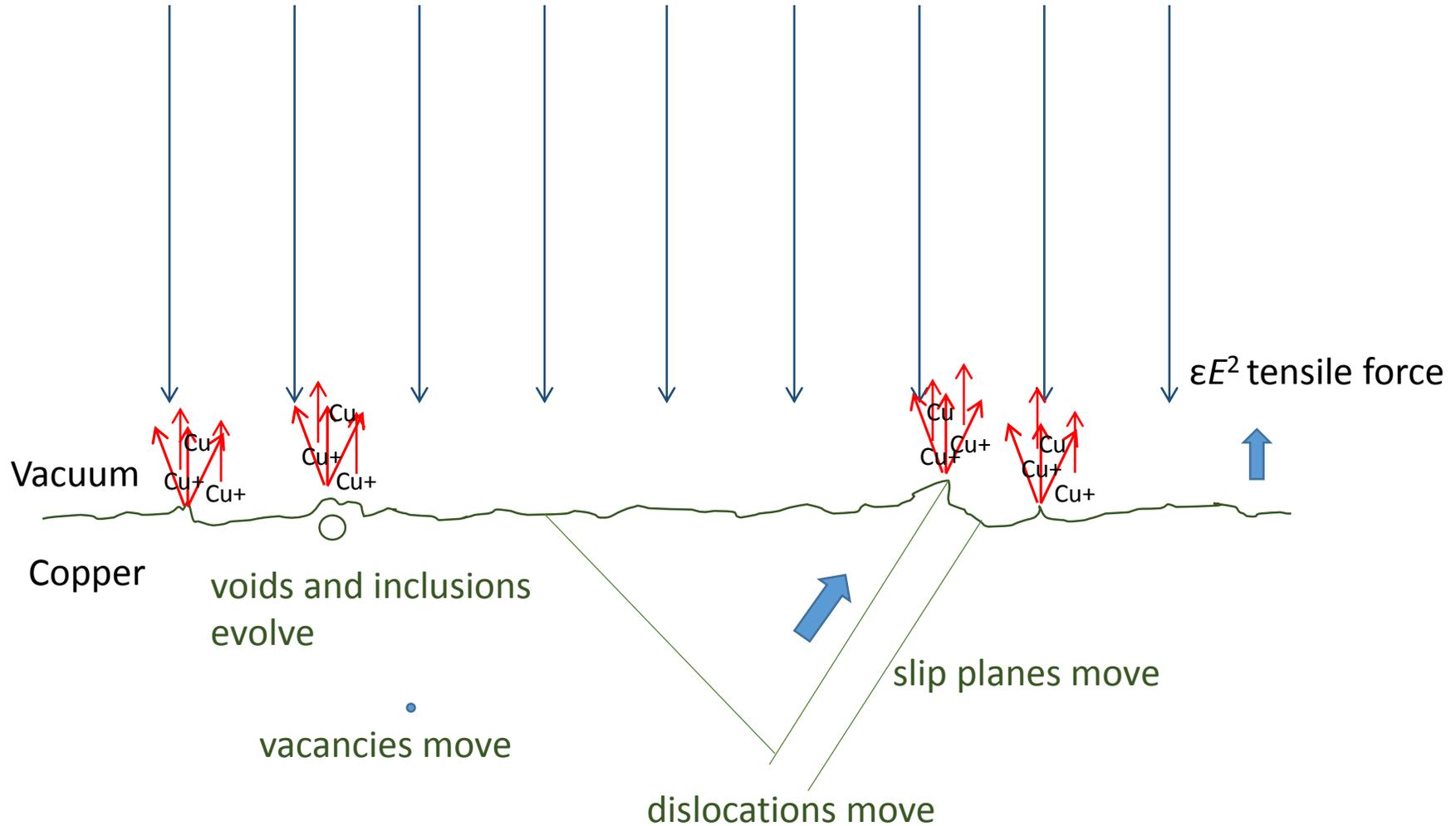


The copper atoms are ionized by the field emission current. the positively charged ions head to the surface and the electrons add to the emission current.





The copper ions hit the surface and sputter more copper in addition to that produced at by the original emission process.





One of these emission points, on some rf or dc pulse, at some point passes a threshold and the process runs away. We will now switch to a computer simulation of the run-away process.

